

# Hiroshi Funakubo

## List of Publications by Year in Descending Order

**Source:** <https://exaly.com/author-pdf/2924762/hiroshi-funakubo-publications-by-year.pdf>  
**Version:** 2024-04-10

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.  
The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

665 papers	10,294 citations	46 h-index	76 g-index
707 ext. papers	11,219 ext. citations	2.3 avg, IF	6.05 L-index

#	Paper	IF	Citations
665	Domain structures induced by tensile thermal strain in epitaxial PbTiO <sub>3</sub> films on silicon substrates. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 035301	2.5	1
664	Polar-axis-oriented epitaxial tetragonal (Bi,K)TiO <sub>3</sub> films with large remanent polarization deposited below Curie temperature by a hydrothermal method. <i>Applied Physics Letters</i> , <b>2022</b> , 120, 022903	3.4	2
663	Lower-temperature processing of potassium niobate films by microwave-assisted hydrothermal deposition technique. <i>Journal of the Ceramic Society of Japan</i> , <b>2022</b> , 130, 123-130	1	
662	Film thickness dependence of ferroelectric properties in polar-axis-oriented epitaxial tetragonal (Bi,K)TiO <sub>3</sub> films prepared by hydrothermal method. <i>AIP Advances</i> , <b>2022</b> , 12, 035241	1.5	0
661	Ferroelectric and piezoelectric properties of 100 nm-thick CeO <sub>2</sub> -HfO <sub>2</sub> epitaxial films. <i>Applied Physics Letters</i> , <b>2022</b> , 120, 132901	3.4	1
660	Thickness dependence of phase stability in epitaxial (Hf <sub>x</sub> Zr <sub>1-x</sub> )O <sub>2</sub> films. <i>Physical Review Materials</i> , <b>2021</b> , 5,	3.2	2
659	Large Piezoelectric Response in Lead-Free (BiNa)TiO-Based Perovskite Thin Films by Ferroelastic Domain Switching: Beyond the Morphotropic Phase Boundary Paradigm. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 57532-57539	9.5	0
658	Demonstration of ferroelectricity in ScGaN thin film using sputtering method. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 172901	3.4	1
657	Composition dependencies of crystal structure and electrical properties of epitaxial tetragonal (Bi, Na)TiO <sub>3</sub> BaTiO <sub>3</sub> films grown on (100)cSrRuO <sub>3</sub> /(100)SrTiO <sub>3</sub> substrates by pulsed laser depositions. <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 134102	2.5	1
656	Electric-Field-Induced Ferroelectricity in 5%Y-doped Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> : Transformation from the Paraelectric Tetragonal Phase to the Ferroelectric Orthorhombic Phase. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2021</b> , 15, 2000589	2.5	9
655	Preparation of 100 nm thick Y-doped HfO <sub>2</sub> ferroelectric films on (111)Pt/TiO <sub>2</sub> /SiO <sub>2</sub> /(001)Si substrates by a sputtering method and their ferroelectric and piezoelectric properties. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, 031009	1.4	5
654	Large thermal hysteresis of ferroelectric transition in HfO <sub>2</sub> -based ferroelectric films. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 112903	3.4	8
653	Electric-Field-Induced Ferroelectricity in 5%Y-doped Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> : Transformation from the Paraelectric Tetragonal Phase to the Ferroelectric Orthorhombic Phase. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2021</b> , 15, 2170023	2.5	1
652	Comprehensive Study on the Kinetic Formation of the Orthorhombic Ferroelectric Phase in Epitaxial Y-Doped Ferroelectric HfO <sub>2</sub> Thin Films. <i>ACS Applied Electronic Materials</i> , <b>2021</b> , 3, 3123-3130	4	10
651	Thermal stability of self-polarization in a (K,Na)NbO <sub>3</sub> film prepared by the hydrothermal method. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SFFB03	1.4	0
650	Growth of 0.1(Bi,Na)TiO <sub>3</sub> 0.9BaTiO <sub>3</sub> epitaxial films by pulsed laser deposition and their electric properties. <i>Journal of the Ceramic Society of Japan</i> , <b>2021</b> , 129, 337-342	1	
649	Impact of Deposition Temperature on Crystal Structure and Ferroelectric Properties of (Al <sub>1-x</sub> Sc <sub>x</sub> )N Films Prepared by Sputtering Method. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2021</b> , 218, 2100302	1.6	1

648	Autonomous Experiments in Scanning Probe Microscopy and Spectroscopy: Choosing Where to Explore Polarization Dynamics in Ferroelectrics. <i>ACS Nano</i> , <b>2021</b> ,	16.7	8
647	Influence of cooling rate on ferroelastic domain structure for epitaxial (100)/(001)-oriented Pb(Zr, Ti)O <sub>3</sub> thin films under tensile strain. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SFFB07	1.4	1
646	High-precision local C <sub>V</sub> mapping for ferroelectrics using principal component analysis. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SFFB09	1.4	0
645	Thickness scaling of (Al <sub>0.8</sub> Sc <sub>0.2</sub> )N films with remanent polarization beyond 100 $\mu$ m around 10 $\mu$ m in thickness. <i>Applied Physics Express</i> , <b>2021</b> , 14, 105501	2.4	8
644	Domain structure transition in compressively strained (100)/(001) epitaxial tetragonal PZT film. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 024101	2.5	1
643	Epitaxial Crystal Growth of Bismuth Silicate Driven by Fluorite-like Layers. <i>Crystal Growth and Design</i> , <b>2020</b> , 20, 7163-7169	3.5	0
642	Structural and electrical characterization of hydrothermally deposited piezoelectric (K,Na)(Nb,Ta)O <sub>3</sub> thick films. <i>Journal of Materials Science</i> , <b>2020</b> , 55, 8829-8842	4.3	4
641	Fabrication and characterization of (CaxSr1-x)Si <sub>2</sub> films prepared by co-sputtering method. <i>MRS Advances</i> , <b>2020</b> , 5, 451-458	0.7	
640	Preparation of iridium metal films by spray chemical vapor deposition. <i>MRS Advances</i> , <b>2020</b> , 5, 1681-1685	0.7	0
639	Large Electromechanical Responses Driven by Electrically Induced Dense Ferroelastic Domains: Beyond Morphotropic Phase Boundaries. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 1908-1916	4	5
638	Fabrication and characterization of ReO <sub>3</sub> -type dielectric films. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 4680-4684	7.1	
637	Temperature dependence on the domain structure of epitaxial PbTiO <sub>3</sub> films grown on single crystal substrates with different lattice parameters. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SPPB01	1.4	5
636	NiSi <sub>2</sub> as a bottom electrode for enhanced endurance of ferroelectric Y-doped HfO <sub>2</sub> thin films. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SGGB06	1.4	1
635	Thickness- and orientation- dependences of Curie temperature in ferroelectric epitaxial Y doped HfO <sub>2</sub> films. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SGGB04	1.4	17
634	Thermoelectric (Ba x Sr1-x)Si <sub>2</sub> films prepared by sputtering method over the barium solubility limit. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SFFB02	1.4	1
633	Preparation of near-1- $\mu$ m-thick {100}-oriented epitaxial Y-doped HfO <sub>2</sub> ferroelectric films on (100)Si substrates by a radio-frequency magnetron sputtering method. <i>Journal of the Ceramic Society of Japan</i> , <b>2020</b> , 128, 539-543	1	7
632	High yield preparation of (100)c-oriented (K,Na)NbO <sub>3</sub> thick films by hydrothermal method using amorphous niobium source. <i>Journal of the Ceramic Society of Japan</i> , <b>2020</b> , 128, 512-517	1	4
631	Rapid deposition of (K,Na)NbO <sub>3</sub> thick films using microwave-assisted hydrothermal technique. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SPPB02	1.4	4

630	Dependency of direct and inverse transverse piezoelectric properties on composition in self-polarized epitaxial $(K_{1-x}Na_x)NbO_3$ films grown via a hydrothermal method. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SPPC03	1.4	2
629	Crystal structure, ferroelectric and piezoelectric properties of epitaxial $(1-x)(Bi_{0.5}Na_{0.5})TiO_3-x(Bi_{0.5}K_{0.5})TiO_3$ films grown by hydrothermal method. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SPPB10	1.4	2
628	Optimization of deposition conditions of yttrium doped-SrZrO <sub>3</sub> thin films fabricated by pulsed laser deposition. <i>Journal of the Ceramic Society of Japan</i> , <b>2020</b> , 128, 436-440	1	1
627	Room-temperature deposition of ferroelectric HfO <sub>2</sub> -based films by the sputtering method. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 062901	3.4	18
626	Local CVM mapping for ferroelectrics using scanning nonlinear dielectric microscopy. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 244105	2.5	1
625	Epitaxial growth of Mg <sub>2</sub> Si films on (111) Si substrates covered with epitaxial SiC layers. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SF1001	1.4	3
624	Good piezoelectricity of self-polarized thick epitaxial (K,Na)NbO <sub>3</sub> films grown below the Curie temperature (240 °C) using a hydrothermal method. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 142903	3.4	2
623	Effects of deposition conditions on the ferroelectric properties of (Al <sub>1-x</sub> Sc <sub>x</sub> )N thin films. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 114103	2.5	58
622	Barkhausen noise analysis of thin film ferroelectrics. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 012902	3.4	1
621	Dynamic Manipulation in Piezoresponse Force Microscopy: Creating Nonequilibrium Phases with Large Electromechanical Response. <i>ACS Nano</i> , <b>2020</b> , 14, 10569-10577	16.7	7
620	Enhanced intrinsic piezoelectric response in (001)-epitaxial single c-domain Pb(Zr,Ti)O <sub>3</sub> nanorods. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 042905	3.4	1
619	Composition Dependence of Crystal Structures and Electrical Properties of Ca-Mg-Si Films Prepared by Sputtering. <i>Journal of Electronic Materials</i> , <b>2020</b> , 49, 7509-7517	1.9	0
618	Tensor factorization for elucidating mechanisms of piezoresponse relaxation via dynamic Piezoresponse Force Spectroscopy. <i>Npj Computational Materials</i> , <b>2020</b> , 6,	10.9	1
617	Bayesian inference in band excitation scanning probe microscopy for optimal dynamic model selection in imaging. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 054105	2.5	4
616	Modeling and Design of a New Piezoelectronic Transistor for Ultralow-Voltage High-Speed Integrated Circuits. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 3852-3860	2.9	
615	Effect of Ta-substitution on the deposition of (K,Na)(Nb,Ta)O <sub>3</sub> films by hydrothermal method. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SLLB12	1.4	6
614	Growth of epitaxial (K, Na)NbO <sub>3</sub> films with various orientations by hydrothermal method and their properties. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SLLB14	1.4	10
613	Ferroelastic domain motion by pulsed electric field in (111)/(111̄) rhombohedral epitaxial Pb(Zr <sub>0.65</sub> Ti <sub>0.35</sub> )O <sub>3</sub> thin films: Fast switching and relaxation. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	1

612	Effects of starting materials on the deposition behavior of hydrothermally synthesized {1 0 0}-oriented epitaxial (K,Na)NbO <sub>3</sub> thick films and their ferroelectric and piezoelectric properties. <i>Journal of Crystal Growth</i> , <b>2019</b> , 511, 1-7	1.6	9
611	Impact of stress on the crystal structural nonuniformity along the film thickness direction by microfabrication of Pb(Zr,Ti)O <sub>3</sub> islands with morphotropic phase boundary composition. <i>Journal of the Ceramic Society of Japan</i> , <b>2019</b> , 127, 123-126	1	3
610	Formation of the orthorhombic phase in CeO <sub>2</sub> -HfO <sub>2</sub> solid solution epitaxial thin films and their ferroelectric properties. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 232902	3.4	14
609	Kinetics of interfacial microstructural variation across insulator-thermoelectric semiconductor interface and its effects on thermoelectric properties of magnesium silicide thin films. <i>Materialia</i> , <b>2019</b> , 7, 100375	3.2	
608	Origin of giant negative piezoelectricity in a layered van der Waals ferroelectric. <i>Science Advances</i> , <b>2019</b> , 5, eaav3780	14.3	74
607	Preparation of CaMgSi and Ca <sub>7</sub> Mg <sub>7.25</sub> Si <sub>14</sub> single phase films and their thermoelectric properties. <i>MRS Advances</i> , <b>2019</b> , 4, 1503-1508	0.7	2
606	Strain-induced resistance change in V <sub>2</sub> O <sub>3</sub> films on piezoelectric ceramic disks. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 115102	2.5	10
605	Effects of heat treatment and in situ high-temperature X-ray diffraction study on the formation of ferroelectric epitaxial Y-doped HfO <sub>2</sub> film. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SB09	1.4	19
604	Epitaxial Growth of Doped HfO <sub>2</sub> Ferroelectric Materials <b>2019</b> , 173-192		2
603	Structural Origin of Temperature-Dependent Ferroelectricity <b>2019</b> , 193-216		2
602	Ferroelectric properties of epitaxial Bi <sub>2</sub> SiO <sub>5</sub> thin films grown on SrTiO <sub>3</sub> substrates with various orientations. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SLLB04	1.4	2
601	Growth of (110)-one-axis-oriented perovskite-type oxide thin films with local epitaxy on (111)SrTiO <sub>3</sub> single crystal substrates. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SLLB01	1.4	
600	Ferroelectricity in YO <sub>1.5</sub> -HfO <sub>2</sub> films around 1 $\mu$ m in thickness. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 032901	3.4	36
599	Evaluation of phase and thermoelectric properties of thin film SrSi <sub>2</sub> . <i>Journal of the Ceramic Society of Japan</i> , <b>2019</b> , 127, 394-398	1	4
598	Electric field-induced change in the crystal structure of MOCVD-Pb(Zr,Ti)O <sub>3</sub> films near the phase boundary. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SLLB07	1.4	2
597	Epitaxial growth of (Bi,K)TiO <sub>3</sub> -Bi(Mg,Ti)O <sub>3</sub> (001) films and their ferroelectric and piezoelectric properties. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SLLB13	1.4	1
596	Low-temperature deposition of Li substituted (K,Na)NbO <sub>3</sub> films by a hydrothermal method and their structural and ferroelectric properties. <i>Journal of the Ceramic Society of Japan</i> , <b>2019</b> , 127, 388-393	1	5
595	Electric-Field-Driven Nanosecond Ferroelastic-Domain Switching Dynamics in Epitaxial Pb(Zr,Ti)O <sub>3</sub> Film. <i>Physical Review Letters</i> , <b>2019</b> , 123, 217601	7.4	11

594	Deposition of orientation-controlled thick (K,Na)NbO <sub>3</sub> films on metal substrates by repeated hydrothermal deposition technique. <i>Journal of the Ceramic Society of Japan</i> , <b>2019</b> , 127, 478-484	1	5
593	Superdomain structure and high conductivity at the vertices in the (111)-oriented epitaxial tetragonal Pb(Zr,Ti)O <sub>3</sub> thin film. <i>Current Applied Physics</i> , <b>2019</b> , 19, 418-423	2.6	5
592	Growth of epitaxial bismuth ruthenate pyrochlore films on yttria-stabilized zirconia (YSZ) and YSZ-buffered Si substrates by metal-organic chemical vapor deposition. <i>Thin Solid Films</i> , <b>2019</b> , 669, 471-474	2.2	0
591	MOCVD growth of EFeSi <sub>2</sub> film on modified Si surface by silver and enhancement of luminescence. <i>Journal of Crystal Growth</i> , <b>2019</b> , 506, 131-134	1.6	1
590	Control of p- and n-type Conduction in Thermoelectric Non-doped Mg <sub>2</sub> Si Thin Films Prepared by Sputtering Method. <i>MRS Advances</i> , <b>2018</b> , 3, 1355-1359	0.7	4
589	Growth of (111)-oriented epitaxial magnesium silicide (Mg <sub>2</sub> Si) films on (001) Al <sub>2</sub> O <sub>3</sub> substrates by RF magnetron sputtering and their properties. <i>Journal of Materials Science</i> , <b>2018</b> , 53, 5151-5158	4.3	6
588	Hydrothermal Deposition of KNbO <sub>3</sub> Films on Metal Substrates having Three-Dimensional Structure. <i>Funtai Oyobi Fumatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy</i> , <b>2018</b> , 65, 673-677	0.2	
587	Thickness and temperature dependences of dielectric properties of {111}-oriented epitaxial Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> and 0.6Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> ·0.4PbTiO <sub>3</sub> films. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 0902BA	1.4	
586	Evaluation of strain components in PbTiO <sub>3</sub> thin films by micro-Raman spectroscopy. <i>Journal of the Ceramic Society of Japan</i> , <b>2018</b> , 126, 936-939	1	
585	On the Use of <sup>31</sup> Mg for EDetected NMR Studies of Solids <b>2018</b> ,		1
584	Ferroelectricity mediated by ferroelastic domain switching in HfO <sub>2</sub> -based epitaxial thin films. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 212901	3.4	49
583	Formation of polar phase in Fe-doped ZrO <sub>2</sub> epitaxial thin films. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 262903	3.4	7
582	Metal-insulator transition in V <sub>2</sub> O <sub>3</sub> thin film caused by tip-induced strain. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 241603	3.4	9
581	Domain structure transition from two to three dimensions in tensile strained (100)/(001)-oriented epitaxial tetragonal PZT film. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 132905	3.4	6
580	Epitaxial ferroelectric Y-doped HfO <sub>2</sub> film grown by the RF magnetron sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 11UF15	1.4	10
579	Domain orientation relationship of orthorhombic and coexisting monoclinic phases of YO <sub>1.5</sub> -doped HfO <sub>2</sub> epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 11UF16	1.4	13
578	Crystallization behavior and ferroelectric property of HfO <sub>2</sub> /ZrO <sub>2</sub> films fabricated by chemical solution deposition. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 11UF06	1.4	14
577	Thickness-dependent crystal structure and electric properties of epitaxial ferroelectric Y <sub>2</sub> O <sub>3</sub> -HfO <sub>2</sub> films. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 102901	3.4	39



576	Fabrication of ferroelectric Fe doped HfO <sub>2</sub> epitaxial thin films by ion-beam sputtering method and their characterization. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 11UF02	1.4	12
575	Epitaxial growth of perovskite-type oxide thin film on (111)SrTiO <sub>3</sub> substrate using (101)PdO as a buffer layer. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 11UF04	1.4	1
574	Stability of the orthorhombic phase in (111)-oriented YO <sub>1.5</sub> -substituted HfO <sub>2</sub> films. <i>Journal of the Ceramic Society of Japan</i> , <b>2018</b> , 126, 269-275	1	6
573	Preparation of {001}c-oriented epitaxial (K, Na)NbO <sub>3</sub> thick films by repeated hydrothermal deposition technique. <i>Journal of the Ceramic Society of Japan</i> , <b>2018</b> , 126, 281-285	1	5
572	Time response demonstration of in situ lattice deformation under an applied electric field by synchrotron-based time-resolved X-ray diffraction in polar-axis-oriented epitaxial Pb(Zr,Ti)O <sub>3</sub> film. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 0902B8	1.4	2
571	Solid-solution thin films of ternary BaTiO <sub>3</sub> Bi(Mg <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> BiFeO <sub>3</sub> system epitaxially grown on SrRuO <sub>3</sub> //SrTiO <sub>3</sub> substrates via chemical solution process. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 0902B5	1.4	0
570	The microstructural evolution in high sodium epitaxial sodium potassium niobate films deposited by low-temperature hydro-thermal method. <i>Journal of Materials Science</i> , <b>2017</b> , 52, 6950-6961	4.3	2
569	Preparation of preferentially (111)-oriented Mg <sub>2</sub> Si thin films on (001)Al <sub>2</sub> O <sub>3</sub> and (100)CaF <sub>2</sub> substrates and their thermoelectric properties. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 05DC02	1.4	6
568	Crystal structure and dielectric/ferroelectric properties of CSD-derived HfO <sub>2</sub> -ZrO <sub>2</sub> solid solution films. <i>Ceramics International</i> , <b>2017</b> , 43, S501-S505	5.1	16
567	Asymmetry in mechanical polarization switching. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 222903	3.4	13
566	Effect of in-plane tensile strain in (100)/(001)-oriented epitaxial PbTiO <sub>3</sub> films on their phase transition temperature and tetragonal distortion. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 122902	3.4	8
565	Synthesis and Photocatalytic Properties of Iron Disilicide/SiC Composite Powder. <i>MRS Advances</i> , <b>2017</b> , 2, 471-476	0.7	2
564	Direct Imaging of the Relaxation of Individual Ferroelectric Interfaces in a Tensile-Strained Film. <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1600508	6.4	7
563	Probing Oxygen Vacancies in BaTiO <sub>3</sub> Powders and Single Crystals by Micro-Raman Scattering. <i>Advanced Structured Materials</i> , <b>2017</b> , 65-75	0.6	
562	Effect of the film thickness on the crystal structure and ferroelectric properties of (Hf <sub>0.5</sub> Zr <sub>0.5</sub> )O <sub>2</sub> thin films deposited on various substrates. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 70, 239-245	4.3	29
561	Effect of microstructures on electrical conduction properties of FeSi <sub>2</sub> epitaxial films. <i>Journal of Crystal Growth</i> , <b>2017</b> , 468, 744-748	1.6	1
560	Experimental study of effect of strain on electrocaloric effect in (001)-epitaxial (Ba,Sr)TiO <sub>3</sub> thin films. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 10PF15	1.4	4
559	Dynamic observation of ferroelectric domain switching using scanning nonlinear dielectric microscopy. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 10PF16	1.4	4

558	Characterization of (111)-oriented epitaxial (K <sub>0.5</sub> Na <sub>0.5</sub> )NbO <sub>3</sub> thick films deposited by hydrothermal method. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 10PF04	1.4	9
557	Electric-field-induced lattice distortion in epitaxial BiFeO <sub>3</sub> thin films as determined by in situ time-resolved x-ray diffraction. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 082907	3.4	2
556	In-situ observation of ultrafast 90° domain switching under application of an electric field in (100)/(001)-oriented tetragonal epitaxial Pb(ZrTi)O thin films. <i>Scientific Reports</i> , <b>2017</b> , 7, 9641	4.9	19
555	Fabrication and characterization of {110}-oriented Pb(Zr,Ti)O <sub>3</sub> thin films on Pt/SiO <sub>2</sub> /Si substrates using PdO//Pd buffer layer. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 10PF09	1.4	1
554	In-plane orientation and composition dependences of crystal structure and electrical properties of {100}-oriented Pb(Zr,Ti)O <sub>3</sub> films grown on (100) Si substrates by metal organic chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 10PF12	1.4	3
553	Charge screening strategy for domain pattern control in nano-scale ferroelectric systems. <i>Scientific Reports</i> , <b>2017</b> , 7, 5236	4.9	12
552	Epitaxial growth of YO <sub>1.5</sub> doped HfO <sub>2</sub> films on (100) YSZ substrates with various concentrations. <i>Ferroelectrics</i> , <b>2017</b> , 512, 105-110	0.6	10
551	Inverse-magnetostriction-induced switching current reduction of STT-MTJs and its application for low-voltage MRAM. <i>Solid-State Electronics</i> , <b>2017</b> , 128, 194-199	1.7	0
550	Effect of substrate type and temperature on the growth of thin Ru films by metal organic chemical vapor deposition. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 70, 73-77	4.3	2
549	Enhancement of photoluminescence from iron disilicide on Si(111) substrates with Au layers by controlling microstructures. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 06HE03	1.4	1
548	Evaluation of oxygen vacancies in ZnO single crystals and powders by micro-Raman spectroscopy. <i>Journal of the Ceramic Society of Japan</i> , <b>2017</b> , 125, 445-448	1	23
547	Indirect measurements of electrocaloric effect in ferroelectric thin films by positive-up-negative-down method. <i>Journal of the Ceramic Society of Japan</i> , <b>2017</b> , 125, 441-444	1	3
546	Orientation change with substrate type and composition in (100)/(001)-oriented epitaxial tetragonal Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> films. <i>Journal of the Ceramic Society of Japan</i> , <b>2017</b> , 125, 458-462	1	3
545	Piezoelectronic transistor for low-voltage high-speed integrated electronics <b>2017</b> ,		2
544	Polarization switching behavior of one-axis-oriented lead zirconate titanate films fabricated on metal oxide nanosheet layer. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 10PF10	1.4	0
543	Development of a novel cell structure for low-temperature SOFC using porous stainless steel support combined with hydrogen permeable Pd layer and thin film proton conductor. <i>Journal of Alloys and Compounds</i> , <b>2016</b> , 654, 171-175	5.7	11
542	Dielectric properties of BaTiO <sub>3</sub> –Bi(Mg <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> films with preferential crystal orientation. <i>Journal of the Ceramic Society of Japan</i> , <b>2016</b> , 124, 648-652	1	2
541	Effects of substrate surface composition and deposition temperature on deposition of flat and continuous Ru thin films. <i>Journal of the Ceramic Society of Japan</i> , <b>2016</b> , 124, 694-696	1	1



540	Enhancement of Dielectric Properties in Epitaxial Bismuth Ferrite/Bismuth Samarium Ferrite Superlattices. <i>Advanced Electronic Materials</i> , <b>2016</b> , 2, 1600170	6.4	7
539	The demonstration of significant ferroelectricity in epitaxial Y-doped HfO <sub>2</sub> film. <i>Scientific Reports</i> , <b>2016</b> , 6, 32931	4.9	153
538	Orientation control of barium titanate films using metal oxide nanosheet layer. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 10TA15	1.4	3
537	Metal-organic chemical vapor deposition growth of FeSi <sub>2</sub> /Si composite powder via vapor-liquid-solid method and its photocatalytic properties. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 06HC02	1.4	3
536	Fabrication of highly (110)-oriented BaCeO <sub>3</sub> -based proton-conductive oxide thin films by RF magnetron sputtering method. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 02BC19	1.4	2
535	Preparation of Ca-Si Films on (001) Al <sub>2</sub> O <sub>3</sub> Substrates by an RF Magnetron Sputtering Method and Their Electrical Properties. <i>Journal of Electronic Materials</i> , <b>2016</b> , 45, 3121-3126	1.9	5
534	Fabrication of Tetragonal Pb(Zr,Ti)O <sub>3</sub> Nanorods by Focused Ion Beam and Characterization of the Domain Structure. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , <b>2016</b> , 63, 1642-1646	3.2	3
533	Growth of {110}-one-axis-oriented perovskite-type oxide films using self-aligned epitaxial (101)PdO/(111) Pd double layers. <i>Thin Solid Films</i> , <b>2016</b> , 599, 133-137	2.2	6
532	Epitaxial growth and photoluminescence properties of FeSi <sub>2</sub> grains using liquid phase obtained by Au-Si eutectic reaction <b>2016</b> ,		1
531	Fabrication of (110)-one-axis-oriented perovskite-type oxide thin films and their application to buffer layer. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 10TA19	1.4	
530	Low temperature MOCVD of Ta <sub>2</sub> O <sub>5</sub> dielectric thin films from Ta[NC(CH <sub>3</sub> ) <sub>3</sub> ][OC(CH <sub>3</sub> ) <sub>3</sub> ] <sub>3</sub> and O <sub>2</sub> . <i>Journal of the Ceramic Society of Japan</i> , <b>2016</b> , 124, 510-514	1	1
529	Thermally stable dielectric responses in uniaxially (001)-oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> nanofilms grown on a Ca <sub>2</sub> Nb <sub>3</sub> O <sub>10</sub> - nanosheet seed layer. <i>Scientific Reports</i> , <b>2016</b> , 6, 20713	4.9	8
528	Composition dependences of crystal structure and electrical properties of epitaxial Pb(Zr,Ti)O <sub>3</sub> films grown on Si and SrTiO <sub>3</sub> substrates. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 10TA08	1.4	1
527	Impact of mechanical stress on ferroelectricity in (Hf <sub>0.5</sub> Zr <sub>0.5</sub> )O <sub>2</sub> thin films. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 262904	3.4	121
526	Simultaneous achievement of high dielectric constant and low temperature dependence of capacitance in (111)-oriented BaTiO <sub>3</sub> -Bi(Mg <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> -BiFeO <sub>3</sub> solid solution thin films. <i>AIP Advances</i> , <b>2016</b> , 6, 015304	1.5	3
525	Crystal structure and compositional analysis of epitaxial (K <sub>0.56</sub> Na <sub>0.44</sub> )NbO <sub>3</sub> films prepared by hydrothermal method. <i>Journal of Materials Research</i> , <b>2016</b> , 31, 693-701	2.5	4
524	Angular dependence of Raman spectrum for Pb(Zr,Ti)O <sub>3</sub> epitaxial films. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 10TC07	1.4	4
523	Growth of (111)-oriented epitaxial and textured ferroelectric Y-doped HfO <sub>2</sub> films for downscaled devices. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 112901	3.4	54

522	Orientation control and domain structure analysis of {100}-oriented epitaxial ferroelectric orthorhombic HfO <sub>2</sub> -based thin films. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 134101	2.5	42
521	Formation of (111) orientation-controlled ferroelectric orthorhombic HfO <sub>2</sub> thin films from solid phase via annealing. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 052903	3.4	29
520	Large irreversible non-180° domain switching after poling treatment in Pb(Zr, Ti)O <sub>3</sub> films. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 212901	3.4	9
519	Fabrication and characterization of (111)-epitaxial Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> /Pb(Zr <sub>0.65</sub> Ti <sub>0.35</sub> )O <sub>3</sub> artificial superlattice thin films. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 10TA20	1.4	1
518	High temperature stability of the dielectric and insulating properties of Ca(Ti, Zr)SiO <sub>5</sub> ceramics. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 062902	3.4	10
517	Growth of epitaxial tetragonal (Bi,K)TiO <sub>3</sub> films and their ferroelectric and piezoelectric properties. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 10TA13	1.4	6
516	Control of Iron Disilicide Crystal Structure by Using Liquid Phase Obtained by Au-Si Eutectic Reaction. <i>Materials Research Society Symposia Proceedings</i> , <b>2015</b> , 1760, 139		3
515	Ba(Zr Ti)O <sub>3</sub> thin films for tunable microwave applications. <i>Ceramics International</i> , <b>2015</b> , 41, S323-S330	5.1	5
514	Effects of porous flow field type separators using sintered Ni-based alloy powders on interfacial contact resistances and fuel cell performances. <i>Energy</i> , <b>2015</b> , 87, 134-141	7.9	8
513	Epitaxial growth of luminescent FeSi <sub>2</sub> on modified Si(111) surface by silver <b>2015</b> ,		1
512	Chemical Fluid Deposition of Hf-Zr-O-based Thin Films using Supercritical Carbon Dioxide Fluid. <i>Materials Research Society Symposia Proceedings</i> , <b>2015</b> , 1729, 99-104		1
511	Epitaxial PbZr <sub>x</sub> Ti <sub>1-x</sub> O <sub>3</sub> Ferroelectric Bilayers with Giant Electromechanical Properties. <i>Advanced Materials Interfaces</i> , <b>2015</b> , 2, 1500075	4.6	13
510	Growth and evaluation of epitaxial BaTiO <sub>3</sub> thin films of less than 100 nm thickness by metal-organic chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 035501	1.4	2
509	Pulse poling within 1 second enhance the piezoelectric property of PZT thin films <b>2015</b> ,		2
508	Suppressed polar distortion with enhanced Curie temperature in in-plane 90° domain structure of a-axis oriented PbTiO <sub>3</sub> Film. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 042905	3.4	26
507	Orientation and film thickness dependencies of (100)- and (111)-oriented epitaxial Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> films grown by metal organic chemical vapor deposition. <i>Journal of Materiomics</i> , <b>2015</b> , 1, 188-195	6.7	3
506	Stabilizing the ferroelectric phase in doped hafnium oxide. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 072006	2.5	294
505	Evaluation of oxygen vacancy in ZnO using Raman spectroscopy <b>2015</b> ,		4

504	Growth of epitaxial orthorhombic YO <sub>1.5</sub> -substituted HfO <sub>2</sub> thin film. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 032910	3.4	102
503	Polar-axis-oriented crystal growth of tetragonal PZT films on stainless steel substrate using pseudo-perovskite nanosheet buffer layer. <i>AIP Advances</i> , <b>2015</b> , 5, 077139	1.5	3
502	Photoluminescent iron disilicide on modified Si surface by using silver. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 07JB04	1.4	4
501	Fabrication of (100)c-oriented Mn-doped bismuth ferrite films on silicon and stainless steel substrates using calcium niobate nanosheets. <i>Journal of the Ceramic Society of Japan</i> , <b>2015</b> , 123, 322-328 <sup>1</sup>		4
500	Domain structure of tetragonal Pb(Zr,Ti)O <sub>3</sub> nanorods and its size dependence. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 10NA07	1.4	7
499	Phase transitions associated with competing order parameters in compressively strained SrTiO <sub>3</sub> thin films. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	10
498	Intermediate-temperature operation of solid oxide fuel cells (IT-SOFCs) with thin film proton conductive electrolyte. <i>Journal of Physics: Conference Series</i> , <b>2015</b> , 660, 012057	0.3	3
497	Transport properties and c/a ratio of V <sub>2</sub> O <sub>3</sub> thin films grown on C- and R-plane sapphire substrates by pulsed laser deposition. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 241901	3.4	32
496	Negligible substrate clamping effect on piezoelectric response in (111)-epitaxial tetragonal Pb(Zr, Ti)O <sub>3</sub> films. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 072012	2.5	16
495	Orientation control of epitaxial tetragonal Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> thin films grown on (100)KTaO <sub>3</sub> substrates by tuning the Zr/(Zr + Ti) ratio. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 022902	3.4	10
494	Fabrication and characterization of (110)-oriented (Ba <sub>0.5</sub> Sr <sub>0.5</sub> )TiO <sub>3</sub> thin films using PdO//Pd buffer layer. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 10NA15	1.4	5
493	Effect of incubation time on preparation of continuous and flat Ru films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2015</b> , 33, 01A149	2.9	5
492	Structural characterization of epitaxial Mg <sub>2</sub> Si films grown on MgO and MgO-buffered Al <sub>2</sub> O <sub>3</sub> substrates. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 07JC01	1.4	2
491	Fabrication of tetragonal Pb(Zr,Ti)O <sub>3</sub> nanorods by focused ion beam and characterization of the domain structure <b>2015</b> ,		2
490	Vibration-energy-harvesting properties of hydrothermally synthesized (K,Na)NbO <sub>3</sub> films deposited on flexible metal foil substrates. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 10ND06	1.4	14
489	Contribution of oxygen vacancies to the ferroelectric behavior of Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> thin films. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 112904	3.4	55
488	Photocatalytic hydrogen evolution over Iron silicide under infrared-light irradiation. <i>Chemical Communications</i> , <b>2015</b> , 51, 2818-20	5.8	20
487	Interfacial dislocations in (111) oriented (Ba <sub>0.7</sub> Sr <sub>0.3</sub> )TiO <sub>3</sub> films on SrTiO <sub>3</sub> single crystal. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 141605	3.4	2

486	Electrical Properties of (110)-Oriented Nondoped Mg <sub>2</sub> Si Films with p-Type Conduction Prepared by RF Magnetron Sputtering Method. <i>Journal of Electronic Materials</i> , <b>2014</b> , 43, 2269-2273	1.9	20
485	Photovoltaic properties of Si-based quantum-dot-sensitized solar cells prepared using laser plasma in liquid. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 010208	1.4	6
484	Measurement of transient photoabsorption and photocurrent of BiFeO <sub>3</sub> thin films: Evidence for long-lived trapped photocarriers. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	24
483	Lead- and alkali-metal-free BaTiO <sub>3</sub> Bi(Mg <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> BiFeO <sub>3</sub> solid-solution thin films with high dielectric constant prepared on Si substrates by solution-based method. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 09PA12	1.4	4
482	Structural and tunable characteristics of Ba(Zr x Ti <sub>1-x</sub> )O <sub>3</sub> films prepared by RF-magnetron sputtering using a metal target. <i>Journal of the Korean Physical Society</i> , <b>2014</b> , 65, 275-280	0.6	1
481	Effects of the porous structures in the porous flow field type separators on fuel cell performances. <i>International Journal of Hydrogen Energy</i> , <b>2014</b> , 39, 15072-15080	6.7	16
480	Dielectric property of (001) one-axis oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> -based thin films and their temperature dependence. <i>Journal of the Ceramic Society of Japan</i> , <b>2014</b> , 122, 477-482	1	2
479	Columnar grain boundary coherence in yttria-stabilized zirconia thin film: effects on ionic conductivity. <i>Journal of the Ceramic Society of Japan</i> , <b>2014</b> , 122, 72-77	1	11
478	Chemical and structural effects on ionic conductivity at columnar grain boundaries in yttria-stabilized zirconia thin films. <i>Journal of the Ceramic Society of Japan</i> , <b>2014</b> , 122, 430-435	1	2
477	Activation of piezoelectric property of PZT thin films by pulse poling. <i>Journal of Physics: Conference Series</i> , <b>2014</b> , 557, 012130	0.3	1
476	Effects of heat treatment on electrical and electromechanical properties of hydrothermally synthesized epitaxial (K <sub>0.51</sub> Na <sub>0.49</sub> )NbO <sub>3</sub> films. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 05FE02	1.4	6
475	Ferroelectric and piezoelectric properties of KNbO <sub>3</sub> films deposited on flexible organic substrate by hydrothermal method. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 09PA10	1.4	12
474	Crystal orientation dependency of ferroelectric property in rhombohedral Pb(Zr,Ti)O <sub>3</sub> films. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 04ED06	1.4	3
473	Interface control of a morphotropic phase boundary in epitaxial samarium modified bismuth ferrite superlattices. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	19
472	Structural and Electrical Properties of Ba(ZrxTi1-x)O3 Films Prepared by RF-magnetron Sputtering Using Metal Targets. <i>Integrated Ferroelectrics</i> , <b>2014</b> , 157, 101-113	0.8	
471	Direct observation of intrinsic piezoelectricity of Pb(Zr,Ti)O <sub>3</sub> by time-resolved x-ray diffraction measurement using single-crystalline films. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 012905	3.4	19
470	In-situ Raman Spectroscopic Investigation of the Effect of Cooling Speed on Domain Formation in PbTiO <sub>3</sub> Films. <i>Integrated Ferroelectrics</i> , <b>2014</b> , 157, 39-46	0.8	
469	Impact of thermal expansion of substrates on phase transition temperature of VO <sub>2</sub> films. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 123510	2.5	21

468	Dependence of $\epsilon_{31}$ on polar axis texture for tetragonal $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ thin films. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 104907	2.5	20
467	Dielectric tunability analysis of pyrochlore $\text{Bi}_{1.5}\text{Zn}_{1.0}\text{Nb}_{1.5}\text{O}_7$ using epitaxial films on pyrochlore $\text{Bi}_2\text{Ru}_2\text{O}_7$ conductive layers. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 022908	3.4	7
466	Impact of pulse poling on static and dynamic ferroelastic-domain contributions in tetragonal $\text{Pb}(\text{Ti}, \text{Zr})\text{O}_3$ films determined by in-situ x-ray diffraction analysis. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 194102	2.5	18
465	Influence of pulse poling on the piezoelectric property of $\text{Pb}(\text{Zr}_{0.52}\text{Ti}_{0.48})\text{O}_3$ thin films. <i>AIP Advances</i> , <b>2014</b> , 4, 117116	1.5	12
464	Low Temperature Preparation of $\text{KNbO}_3$ Films by Hydrothermal Method and Their Characterization. <i>Materials Research Society Symposia Proceedings</i> , <b>2014</b> , 1659, 49-54		3
463	High Temperature Reproducible Preparation of $\text{Mg}_2\text{Si}$ Films on (001) $\text{Al}_2\text{O}_3$ substrates Using RF Magnetron Sputtering Method. <i>Materials Research Society Symposia Proceedings</i> , <b>2014</b> , 1642, 1		6
462	Characterizations of epitaxial $\text{Bi}(\text{Mg}_{1/2}\text{Ti}_{1/2})\text{O}_3\text{Bi}(\text{Zn}_{1/2}\text{Ti}_{1/2})\text{O}_3$ solid solution films grown by pulsed laser deposition. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 05FE06	1.4	2
461	Structural and dielectric properties of $\text{BaTiO}_3\text{Bi}(\text{Mg}_{1/2}\text{Ti}_{1/2})\text{O}_3$ thin films fabricated by chemical solution deposition. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 09PA11	1.4	3
460	Preparation and characterization of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ thin films for high-frequency applications. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 09PB04	1.4	4
459	Ferroelectric and piezoelectric properties of $(\text{K}, \text{Na})\text{NbO}_3$ thick films prepared on metal substrates by hydrothermal method. <i>Journal of the Korean Physical Society</i> , <b>2013</b> , 62, 1055-1059	0.6	16
458	Linear actuation piezoelectric microcantilever using tetragonal composition PZT thin films <b>2013</b> ,		4
457	Laser Wavelength Effect on Size and Morphology of Silicon Nanoparticles Prepared by Laser Ablation in Liquid. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 025001	1.4	31
456	Identification of the Occupation Site of Dy- or Y-Substituted PZT Films and the Correlation Between Occupation Site and Ferroelectric Property. <i>Integrated Ferroelectrics</i> , <b>2013</b> , 141, 1-8	0.8	1
455	Nanoscale Origins of Nonlinear Behavior in Ferroic Thin Films. <i>Advanced Functional Materials</i> , <b>2013</b> , 23, 81-90	15.6	18
454	One-Axis-Oriented Crystal Growth of Lead Zirconate Titanate Thin Films on Metal Substrates Using Perovskite-Type Oxide Nanosheet Layer. <i>Key Engineering Materials</i> , <b>2013</b> , 582, 15-18	0.4	0
453	Analysis of Lattice Defects in an Epitaxial $\text{PbTiO}_3$ Thick Film by Transmission Electron Microscopy. <i>Key Engineering Materials</i> , <b>2013</b> , 566, 171-174	0.4	
452	Epitaxial growth of (010)-oriented $\text{PbFeSi}_2$ film on $\text{Si}(110)$ substrate. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1493, 189-194		1
451	Small-strain (100)/(001)-oriented epitaxial $\text{PbTiO}_3$ films with film thickness ranging from nano- to micrometer order grown on (100) $\text{CaF}_2$ substrates by metal organic chemical vapor deposition. <i>Journal of Materials Research</i> , <b>2013</b> , 28, 696-701	2.5	3



450	Growth of 130 nm Thick Epitaxial KNbO <sub>3</sub> Film by Hydrothermal Method. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1494, 291-296		9
449	Preparation of Bismuth Based Perovskite Oxides and their Electric Properties. <i>Key Engineering Materials</i> , <b>2013</b> , 582, 71-75	0.4	0
448	Direct Observation of Atomic Arrangement around 90° Domain Wall in Lead Titanate Thin Films.. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1515, 1		1
447	Effects of Bipolar Pulse Poling on the Ferroelectric and Piezoelectric Properties of Tetragonal Composition Pb(Zr <sub>0.3</sub> Ti <sub>0.7</sub> )O <sub>3</sub> Thin Films on Microelectromechanical Systems Microcantilevers. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 09KA01	1.4	11
446	Growth of (111) One-Axis-Oriented Bi(Mg <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> Films on (100)Si Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CH09	1.4	4
445	Strain-Stable Nonlinear Dielectric Responses in Pyrochlore Bismuth Zinc Niobate Thin Films. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 09KA13	1.4	2
444	Fabrication of BiFeO <sub>3</sub> -Bi(Zn <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> Solid Solution Thin Films Using Perovskite-Type Oxide Interface Layer. <i>Key Engineering Materials</i> , <b>2013</b> , 566, 163-166	0.4	
443	Squareness Control in Polarization-Electric Field Hysteresis Curves in Rhombohedral Pb(Zr,Ti)O <sub>3</sub> Films. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CD09	1.4	1
442	Phase Boundary Shift by Thermal Strain in 100-Oriented Epitaxial Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> Film Grown on CaF <sub>2</sub> Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 09KA02	1.4	6
441	Nano-Structure around 90° Domain Wall and Elastic Interaction with Misfit Dislocation in PbTiO <sub>3</sub> Thin Film. <i>Key Engineering Materials</i> , <b>2013</b> , 566, 167-170	0.4	1
440	Crystal Structure Analysis of Hydrothermally Synthesized Epitaxial (K <sub>x</sub> Na <sub>1-x</sub> )NbO <sub>3</sub> Films. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 09KA11	1.4	19
439	Unusual 90° domain structure in (2/3)Bi(Zn <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> -(1/3)BiFeO <sub>3</sub> epitaxial films with giant 22% tetragonal distortion. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 042904	3.4	5
438	Control of Volume Fraction of Non-180° Domains by Thermal Strain in Epitaxial Rhombohedral Pb(Zr, Ti)O <sub>3</sub> Thick Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1507, 1		2
437	Crystal Structure Change with Applied Electric Field for (100)/(001)-oriented Polycrystalline Lead Zirconate Titanate Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1507, 1		3
436	Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> Nanowall Growth Driven by Anisotropic Growth Rate and Size Control. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 09KA09	1.4	1
435	Oxygen vacancies in PbTiO <sub>3</sub> thin films probed by resonant Raman spectroscopy. <i>Journal of the Ceramic Society of Japan</i> , <b>2013</b> , 121, 598-601	1	5
434	Composition dependency of crystal structure, electrical and piezoelectric properties for hydrothermally-synthesized 3 μm-thickness (K <sub>x</sub> Na <sub>1-x</sub> )NbO <sub>3</sub> films. <i>Journal of the Ceramic Society of Japan</i> , <b>2013</b> , 121, 627-631	1	18
433	Investigation of PbTiO <sub>3</sub> thin films with reduced and re-oxidized treatment using Raman spectroscopy. <i>Journal of the Ceramic Society of Japan</i> , <b>2013</b> , 121, 859-862	1	4



432	Epitaxial growth of Mg <sub>2</sub> Si films on strontium titanate single crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 1688-1691		6
431	Evaluation of EFeSi <sub>2</sub> /Si-interface using Ag-coating on Si surface. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 1684-1687		4
430	Temperature and electric field stabilities of dielectric and insulating properties for c-axis-oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> films. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 027002	2.5	11
429	Influence of Ba/Sr ratio in compressively-strained (Ba,Sr)TiO <sub>3</sub> (001) films on the ferroelectric phase transition. <i>Journal of the Ceramic Society of Japan</i> , <b>2013</b> , 121, 690-692	1	5
428	Fabrication and Evaluation of One-Axis Oriented Lead Zirconate Titanate Films Using MetalOxide Nanosheet Interface Layer. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 09KA04	1.4	9
427	Preparation of Bismuth-Based Perovskites with Non-integer A and B Site Valence and Their Properties. <i>Transactions of the Materials Research Society of Japan</i> , <b>2013</b> , 38, 49-52	0.2	
426	Stacking faults in an epitaxially grown PbTiO <sub>3</sub> thick film and their size distribution. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2012</b> , 177, 528-531	3.1	1
425	Preparation and Characterization of Ba(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> Thin Films Using Reactive Sputtering Method. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA01	1.4	2
424	Preparation and Characterization of BaTiO <sub>3</sub> Thin Films Using Reactive Sputtering Method with Metal Target. <i>Integrated Ferroelectrics</i> , <b>2012</b> , 133, 42-48	0.8	1
423	Growth of (111)-oriented BaTiO <sub>3</sub> Bi(Mg <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> epitaxial films and their crystal structure and electrical property characterizations. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 084108	2.5	14
422	Complex domain structure in relaxed PbTiO <sub>3</sub> thick films grown on (100)cSrRuO <sub>3</sub> /(100)SrTiO <sub>3</sub> substrates. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 052001	2.5	12
421	Dynamic piezoresponse force microscopy: Spatially resolved probing of polarization dynamics in time and voltage domains. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 052021	2.5	28
420	Effect of point defects on lattice constant in MgO thin film deposited on silicon(0 0 1) substrate. <i>EPJ Applied Physics</i> , <b>2012</b> , 58, 10302	1.1	
419	Film Thickness Dependence of Ferroelectric Properties of (111)-Oriented Epitaxial Bi(Mg <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> Films. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA04	1.4	11
418	Film Thickness Dependence of Crystal Structure in 100-Oriented Epitaxial Pb(Zr <sub>0.65</sub> Ti <sub>0.35</sub> )O <sub>3</sub> Films Grown on Single-Crystal Substrates with Different Thermal Expansion Coefficients. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA14	1.4	5
417	Charge trapping-detrapping induced resistive switching in Ba <sub>0.7</sub> Sr <sub>0.3</sub> TiO <sub>3</sub> . <i>AIP Advances</i> , <b>2012</b> , 2, 032166	1.5	39
416	Investigation of Sputtering Damage in SrRuO <sub>3</sub> Films Prepared by Sputtering with Raman and X-ray Photoemission Spectroscopies. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA19	1.4	
415	Effects of A-Site Occupancy of Bismuth Ions on the Dielectric Tunable Properties of Pyrochlore Bismuth Zinc Niobate Films. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA10	1.4	2

4 <sup>14</sup>	Anisotropic electrical properties in bismuth layer structured dielectrics with natural super lattice structure. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 012907	3.4	2
4 <sup>13</sup>	Molecular Dynamics Simulation of 90° Ferroelectric Domains in PbTiO <sub>3</sub> . <i>Journal of the Physical Society of Japan</i> , <b>2012</b> , 81, 124702	1.5	11
4 <sup>12</sup>	Domain tuning in mixed-phase BiFeO <sub>3</sub> thin films using vicinal substrates. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 202901	3.4	9
4 <sup>11</sup>	A new SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> /CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> thin-film capacitor for excellent electric stability. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , <b>2012</b> , 59, 1888-93	3.2	1
4 <sup>10</sup>	Distribution of Crystal Structure in Epitaxial Pb(Zr <sub>0.42</sub> Ti <sub>0.58</sub> )O <sub>3</sub> Film Grown on (111) c SrRuO <sub>3</sub> /(111)SrTiO <sub>3</sub> Substrate. <i>Integrated Ferroelectrics</i> , <b>2012</b> , 133, 54-60	0.8	
4 <sup>09</sup>	Epitaxial PZT Films for MEMS printing applications. <i>MRS Bulletin</i> , <b>2012</b> , 37, 1030-1038	3.2	4 <sup>0</sup>
4 <sup>08</sup>	Temperature and Frequency Dependencies of Ferroelectric Properties in Rhombohedral Epitaxial Pb(Zr,Ti)O <sub>3</sub> Films with Perfect (111) Orientations Grown on CaF <sub>2</sub> Substrates.. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1397, 65		
4 <sup>07</sup>	1.54 $\mu$ m luminescence of $\Gamma$ -FeSi <sub>2</sub> grown on Au-coated Si substrates. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1396,		1
4 <sup>06</sup>	Noncontact probing method for estimation of ferroelectric properties of PbTiO <sub>3</sub> -based films for microelectromechanical systems. <i>Journal of Materials Research</i> , <b>2012</b> , 27, 1430-1435	2.5	
4 <sup>05</sup>	Preparation and Characterization of Ba(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> Thin Films Using Reactive Sputtering Method. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA01	1.4	5
4 <sup>04</sup>	Film Thickness Dependence of Ferroelectric Properties of (111)-Oriented Epitaxial Bi(Mg <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> Films. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA04	1.4	5
4 <sup>03</sup>	Effects of A-Site Occupancy of Bismuth Ions on the Dielectric Tunable Properties of Pyrochlore Bismuth Zinc Niobate Films. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA10	1.4	2
4 <sup>02</sup>	Film Thickness Dependence of Crystal Structure in 100-Oriented Epitaxial Pb(Zr <sub>0.65</sub> Ti <sub>0.35</sub> )O <sub>3</sub> Films Grown on Single-Crystal Substrates with Different Thermal Expansion Coefficients. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA14	1.4	3
4 <sup>01</sup>	Preparation of InP Nanoparticles by Laser Ablation in Liquid. <i>The Review of Laser Engineering</i> , <b>2012</b> , 40, 117	0	1
4 <sup>00</sup>	Dynamics of Coherent Optical Phonons in PbTiO <sub>3</sub> Excited by Impulsive Stimulated Raman Scattering. <i>Springer Proceedings in Physics</i> , <b>2012</b> , 369-372	0.2	
399	Dielectric Property of Silicate-Doped CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Thin Films. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA16	1.4	
398	Investigation of Sputtering Damage in SrRuO <sub>3</sub> Films Prepared by Sputtering with Raman and X-ray Photoemission Spectroscopies. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 09LA19	1.4	
397	Buffer-layer-enhanced growth of a single-domain LaB <sub>6</sub> (100) epitaxial thin film on a MgO (100) substrate via pulsed laser deposition. <i>Journal of Crystal Growth</i> , <b>2011</b> , 330, 39-42	1.6	6

396	Preferential Crystal Growth of (100)-Oriented BiFeO <sub>3</sub> Films on Si Substrate. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2011</b> , 18, 092033	0.4	4
395	Enhancement of piezoelectric response in (100)/(001) oriented tetragonal Pb(Zr, Ti)O <sub>3</sub> films by controlling tetragonality and volume fraction of the (001) orientation. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 091601	2.5	12
394	Synthesis of Mica Thin Film by Pulsed Laser Deposition. <i>Applied Physics Express</i> , <b>2011</b> , 4, 055502	2.4	1
393	Rapid and high sensitive structure evaluation of ferroelectric films using micro-Raman spectroscopy: In-situ observation of stress accumulation and release in PbTiO <sub>3</sub> films during first cooling process. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2011</b> , 18, 092002	0.4	
392	Intrinsic Characteristics of Bi(Zn <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> -substituted Pb(Zr <sub>0.4</sub> Ti <sub>0.6</sub> )O <sub>3</sub> Thin Films. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2011</b> , 18, 092008	0.4	
391	Fabrication and Evaluation of Mn-Substituted Ba(Cu <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> Ceramics. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2011</b> , 18, 092038	0.4	0
390	Enhancement of magnetization at morphotropic phase boundary in epitaxial BiCoO <sub>3</sub> -BiFeO <sub>3</sub> solid solution films grown on SrTiO <sub>3</sub> (100) substrates. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 07D917	2.5	16
389	Preparation and Characteristics of Bi <sub>0.5</sub> Na <sub>0.5</sub> TiO <sub>3</sub> Single-Crystalline Films by a Solid-State Process. <i>Journal of the American Ceramic Society</i> , <b>2011</b> , 94, 3291-3295	3.8	9
388	Thickness-dependent ferroelectric properties of Mn-doped BiFeO <sub>3</sub> films formed on Pt and SrRuO <sub>3</sub> /Pt electrodes by RF Sputtering. <i>Current Applied Physics</i> , <b>2011</b> , 11, S228-S231	2.6	3
387	Application of synchrotron-based reciprocal-space mapping at a fixed angular position to identification of crystal symmetry of Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> epitaxial thin films. <i>Journal of Applied Crystallography</i> , <b>2011</b> , 44, 385-391	3.8	3
386	Controlled Polarizability of One-Nanometer-Thick Oxide Nanosheets for Tailored, High- $\epsilon$ Nanodielectrics. <i>Advanced Functional Materials</i> , <b>2011</b> , 21, 3482-3487	15.6	65
385	TEM Observation on Ferroelectric Domain Structures of PbTiO <sub>3</sub> Epitaxial Films. <i>Key Engineering Materials</i> , <b>2011</b> , 485, 179-182	0.4	
384	Strong growth orientation dependence of strain relaxation in epitaxial (Ba,Sr)TiO <sub>3</sub> films and the resulting dielectric properties. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 091605	2.5	23
383	High Fatigue Endurance and Large Remanent Polarization in Pt/SrRuO <sub>3</sub> /BiFe <sub>0.95</sub> Mn <sub>0.05</sub> O <sub>3</sub> /SrRuO <sub>3</sub> /Pt Ferroelectric Capacitors Formed on SiO <sub>2</sub> -Coated Si Substrates. <i>Applied Physics Express</i> , <b>2011</b> , 4, 081501	2.4	3
382	Structure Determination and Compositional Modification of Body-Centered Tetragonal PX-Phase Lead Titanate. <i>Chemistry of Materials</i> , <b>2011</b> , 23, 2529-2535	9.6	17
381	Spontaneous polarization estimation from the soft mode in strain-free epitaxial polar axis-oriented Pb(Zr,Ti)O <sub>3</sub> thick films with tetragonal symmetry. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 141914	3.4	21
380	Epitaxial growth of (100)-oriented BiFeSi <sub>2</sub> film on 3C-SiC(100) plane. <i>Journal of Crystal Growth</i> , <b>2011</b> , 316, 10-14	1.6	1
379	Nano-strip grating lines self-organized by a high speed scanning CW laser. <i>Nanotechnology</i> , <b>2011</b> , 22, 175307	3.4	8

378	Comparison of Ferroelectric and Insulating Properties of Mn-Doped BiFeO <sub>3</sub> Films Formed on Pt, SrRuO <sub>3</sub> /Pt, and LaNiO <sub>3</sub> /Pt Bottom Electrodes by Radio-Frequency Sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 051501	1.4	2
377	Growth of Epitaxial 100-Oriented KNbO <sub>3</sub> /NaNbO <sub>3</sub> Solid Solution Films on (100)cSrRuO <sub>3</sub>   (100)SrTiO <sub>3</sub> by Hydrothermal Method and Their Characterization. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 09ND11	1.4	18
376	Ultrafast switching of ferroelastic nanodomains in bilayered ferroelectric thin films. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 182906	3.4	18
375	Improved ferroelectric property of very thin Mn-doped BiFeO <sub>3</sub> films by an inlaid Al <sub>2</sub> O <sub>3</sub> tunnel switch. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 074111	2.5	20
374	Measurement of Piezoelectric Transverse and Longitudinal Displacement with Atomic Force Microscopy for PZT Thick Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2011</b> , 1318, 1		
373	Dielectric Properties of Bismuth Layer-Structured Oxide Thin Films with Preferential Crystal Orientation at High-Temperature. <i>Key Engineering Materials</i> , <b>2011</b> , 485, 191-194	0.4	
372	Configuration and local elastic interaction of ferroelectric domains and misfit dislocation in PbTiO <sub>3</sub> /SrTiO <sub>3</sub> epitaxial thin films. <i>Science and Technology of Advanced Materials</i> , <b>2011</b> , 12, 034413	7.1	37
371	Growth of Orientation-Controlled Epitaxial KNbO <sub>3</sub> Thin Film by Hydrothermal Method. <i>Key Engineering Materials</i> , <b>2011</b> , 485, 199-202	0.4	7
370	Diffraction contrast analysis of 90° and 180° ferroelectric domain structures of PbTiO <sub>3</sub> thin films. <i>Science and Technology of Advanced Materials</i> , <b>2011</b> , 12, 034403	7.1	11
369	Real-space mapping of dynamic phenomena during hysteresis loop measurements: Dynamic switching spectroscopy piezoresponse force microscopy. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 202903	3.4	21
368	Crystal Orientation Control of Bismuth Layer-Structured Dielectric Films Using Interface Layers of Perovskite-Type Oxides. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 09NA04	1.4	11
367	Electronic and Structural Properties of ABO <sub>3</sub> : Role of the B-O Coulomb Repulsions for Ferroelectricity. <i>Materials</i> , <b>2011</b> , 4, 260-273	3.5	17
366	Growth of (111)-Oriented Epitaxial Bi(Mg <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> Films and their Characterization. <i>Key Engineering Materials</i> , <b>2011</b> , 485, 195-198	0.4	7
365	X-ray Diffraction Study of Electric-field-induced Strains in Polycrystalline BiFeO <sub>3</sub> Thin Films at Low Temperature Using Synchrotron Radiation. <i>Journal of the Korean Physical Society</i> , <b>2011</b> , 59, 2556-2559	0.6	3
364	Comparison of Ferroelectric and Insulating Properties of Mn-Doped BiFeO <sub>3</sub> Films Formed on Pt, SrRuO <sub>3</sub> /Pt, and LaNiO <sub>3</sub> /Pt Bottom Electrodes by Radio-Frequency Sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 051501	1.4	3
363	Crystal Orientation Control of Bismuth Layer-Structured Dielectric Films Using Interface Layers of Perovskite-Type Oxides. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 09NA04	1.4	4
362	Growth of Epitaxial 100-Oriented KNbO <sub>3</sub> /NaNbO <sub>3</sub> Solid Solution Films on (100)cSrRuO <sub>3</sub>   (100)SrTiO <sub>3</sub> by Hydrothermal Method and Their Characterization. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 09ND11	1.4	10
361	Dielectric Properties of Highly (001)-Plane Oriented SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Thin Films. <i>Key Engineering Materials</i> , <b>2010</b> , 445, 131-134	0.4	0

360	A-Site-Modified Perovskite Nanosheets and Their Integration into High-Dielectric Thin Films with a Clean Interface. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 09MA01	1.4	10
359	Electrical properties and x-ray photoelectron spectroscopy studies of Bi(Zn <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> doped Pb(Zr <sub>0.4</sub> Ti <sub>0.6</sub> )O <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 084101	2.5	8
358	Large constriction of lattice constant in epitaxial magnesium oxide thin film: Effect of point defects on lattice constant. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 073523	2.5	20
357	Single crystal-like selection rules for unipolar-axis oriented tetragonal Pb(Zr,Ti)O <sub>3</sub> thick epitaxial films. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 111901	3.4	7
356	In situ Raman spectroscopy for characterization of the domain contributions to electrical and piezoelectric responses in Pb(Zr,Ti)O <sub>3</sub> films. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 181907	3.4	16
355	Effect of Grain Size on Mechanical Properties of Full-Dense Pb(Zr,Ti)O <sub>3</sub> Ceramics. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 09MD13	1.4	18
354	Antiferrodistortive Structural Phase Transition in Compressively-Strained Epitaxial SrTiO <sub>3</sub> Film Grown on (La, Sr)(Al, Ta)O <sub>3</sub> Substrate. <i>Integrated Ferroelectrics</i> , <b>2010</b> , 115, 57-62	0.8	5
353	Experimental evidence for orientation property of Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> by manipulating polar axis angle using CaF <sub>2</sub> substrate. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 102905	3.4	24
352	Crystal Structure and Dielectric Property of Bismuth Layer-Structured Dielectric Films with c-Axis Preferential Crystal Orientation. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 09MA02	1.4	13
351	Structural Property and Electric Field Response of a Single Perovskite PbTiO <sub>3</sub> Nanowire Using Micro X-ray Beam. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 09MC09	1.4	3
350	Large Lattice Misfit on Epitaxial Thin Film: Coincidence Site Lattice Expanded on Polar Coordinate System. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 08JE02	1.4	2
349	Effect of Deposition Time on Film Thickness and Their Properties for Hydrothermally-Grown Epitaxial KNbO <sub>3</sub> Thick Films. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 07HF01	1.4	6
348	Effect of Film Thickness and Crystal Orientation on the Constituent Phase in Epitaxial BiFeO <sub>3</sub> /BiCoO <sub>3</sub> Films Grown on SrTiO <sub>3</sub> Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 09MB04	1.4	10
347	Electronic, Structural, and Piezoelectric Properties of BiFe <sub>1-x</sub> Co <sub>x</sub> O <sub>3</sub> . <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 09ME07	1.4	13
346	EVALUATION OF RELATIVE VOLUME FRACTION OF TETRAGONAL PHASE AND RHOMBOHEDRAL PHASE IN Pb(Zr,Ti)O <sub>3</sub> FILM BY RAMAN SPECTROSCOPY. <i>Integrated Ferroelectrics</i> , <b>2010</b> , 112, 33-41	0.8	3
345	Robust high- $\eta$ response in molecularly thin perovskite nanosheets. <i>ACS Nano</i> , <b>2010</b> , 4, 5225-32	16.7	125
344	Engineered interfaces of artificial perovskite oxide superlattices via nanosheet deposition process. <i>ACS Nano</i> , <b>2010</b> , 4, 6673-80	16.7	128
343	Influence of Epitaxial Growth Orientation on Residual Strain and Dielectric Properties of (Ba <sub>0.3</sub> Sr <sub>0.7</sub> )TiO <sub>3</sub> Films Grown on In-Plane Compressive Substrates. <i>Ferroelectrics</i> , <b>2010</b> , 405, 262-267	0.6	7



342	Comparison of BST film microwave tunable devices based on (100) and (111) MgO substrates. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , <b>2010</b> , 57, 2221-7	3.2	4
341	Self-assembled ferroelectric-dielectric nanocomposite films for tunable applications. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2010</b> , 8, 012010	0.4	
340	Orientation control of (001) and (101) in epitaxial tetragonal Pb(Zr,Ti)O <sub>3</sub> films with (100)/(001) and (110)/(101) mixture orientations. <i>Journal of the Ceramic Society of Japan</i> , <b>2010</b> , 118, 627-630	1	16
339	In-situ observation of a MEMS-based Pb(Zr,Ti)O <sub>3</sub> micro cantilever using micro-Raman spectroscopy. <i>Journal of the Ceramic Society of Japan</i> , <b>2010</b> , 118, 644-647	1	
338	In-situ lattice-strain analysis of a ferroelectric thin film under an applied pulse electric field <b>2010</b> ,		17
337	Composition dependence of crystal structure and electrical properties for epitaxial films of Bi(Zn <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> -BiFeO <sub>3</sub> solid solution system. <i>Journal of the Ceramic Society of Japan</i> , <b>2010</b> , 118, 659-663	1	9
336	Piezoelectric anomalies at the ferroelastic phase transitions of lead-free tungsten bronze ferroelectrics. <i>Journal of the Ceramic Society of Japan</i> , <b>2010</b> , 118, 717-721	1	9
335	Growth of polar axis oriented tetragonal Pb(Zr,Ti)O <sub>3</sub> films on CaF <sub>2</sub> substrates with transparent (La <sub>0.07</sub> Sr <sub>0.93</sub> )SnO <sub>3</sub> . <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 3127-3130	1.6	
334	Synchrotron X-ray diffraction study on a single nanowire of PX-phase lead titanate. <i>Journal of the European Ceramic Society</i> , <b>2010</b> , 30, 3259-3262	6	5
333	MOCVD growth and characterization of BiFeO <sub>3</sub> Bi(Zn <sub>1/2</sub> Ti <sub>1/2</sub> )O <sub>3</sub> ferroelectric films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2010</b> , 173, 14-17	3.1	6
332	Electronic and structural properties of : A proposal about the role of Ti 3s and 3p states for ferroelectricity. <i>Solid State Communications</i> , <b>2010</b> , 150, 205-208	1.6	7
331	Impact of 90° Domain Wall Motion in Pb(Zr <sub>0.43</sub> Ti <sub>0.57</sub> )O <sub>3</sub> Film on the Ferroelectricity Induced by an Applied Electric Field. <i>Applied Physics Express</i> , <b>2009</b> , 2, 041401	2.4	9
330	Effect of bottom electrode on dielectric property of sputtered-(Ba,Sr)TiO <sub>3</sub> films. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 061606	2.5	14
329	Raman Spectroscopy Evaluation of Oxygen Vacancy Migration by Electrical Field in Multilayer Ceramic Capacitors. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KF11	1.4	16
328	Crystal structure and electrical property comparisons of epitaxial Pb(Zr,Ti)O <sub>3</sub> thick films grown on (100)CaF <sub>2</sub> and (100)SrTiO <sub>3</sub> substrates. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 061614	2.5	23
327	Composition control and thickness dependence of {100}-oriented epitaxial BiCoO <sub>3</sub> BiFeO <sub>3</sub> films grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 061620	2.5	15
326	Domain structure of (100)/(001)-oriented epitaxial PbTiO <sub>3</sub> thick films with various volume fraction of (001) orientation grown by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 052906	3.4	25
325	Composition Dependency of Epitaxial Pb(Zr,Ti)O <sub>3</sub> Films with Different Film Thickness. <i>Ferroelectrics</i> , <b>2009</b> , 389, 10-17	0.6	5



324	Effect of Incubation Time on Deposition Behavior of Ruthenium Films by MOCVD Using (2,4-Dimethylpentadienyl)(Ethylcyclopentadienyl)Ruthenium. <i>Key Engineering Materials</i> , <b>2009</b> , 421-422, 87-90	0.4	2
323	Ligand Structure Effect on A Divalent Ruthenium Precursor for MOCVD. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1155, 1		1
322	Polarized Raman Study for Epitaxial PZT Thick Film with the Mixture Orientation of (100)/(001). <i>Key Engineering Materials</i> , <b>2009</b> , 421-422, 99-102	0.4	2
321	Determination Factors of Strain-relaxed Complex Domain Structure Observed in Thick Epitaxial Pb (Zr, Ti)O <sub>3</sub> Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1199, 142		1
320	The Effect of Precursor Ligands on the Deposition Characteristics of Ru Films by MOCVD. <i>Electrochemical and Solid-State Letters</i> , <b>2009</b> , 12, D80		12
319	In situ Observation of the Fatigue-Free Piezoelectric Microcantilever by Two-Dimensional X-ray Diffraction. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KA03	1.4	11
318	Electric-Field-Induced Transverse Displacement in Pt/Pb(Zr,Ti)O <sub>3</sub> Film/Pt/Si Structure. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KA04	1.4	1
317	Growth of Epitaxial KNbO <sub>3</sub> Thick Films by Hydrothermal Method and Their Characterization. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KA14	1.4	18
316	Low-Temperature Preparation of (111)-oriented Pb(Zr,Ti)O <sub>3</sub> Films Using Lattice-Matched (111)SrRuO <sub>3</sub> /Pt Bottom Electrode by Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 04C067	1.4	3
315	Piezoelectric Properties of {100}-Oriented Epitaxial BiCoO <sub>3</sub> BiFeO <sub>3</sub> Films Measured Using Synchrotron X-ray Diffraction. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KD06	1.4	10
314	Solution-Based Fabrication of Perovskite Nanosheet Films and Their Dielectric Properties. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KA15	1.4	12
313	Preparation of (001)-Oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> and SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Films Using LaNiO <sub>3</sub> Nucleation Layer on Pt-passivated Si Wafer. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KA10	1.4	7
312	Solution-Based Fabrication of High-k Dielectrics Using Oxide Nanosheets. <i>ECS Transactions</i> , <b>2009</b> , 25, 349-352	1	
311	Good Conformability of Indium-Tin Oxide Thin Films Prepared by Spray Chemical Vapor Deposition. <i>Electrochemical and Solid-State Letters</i> , <b>2009</b> , 12, D42		7
310	Strain-relaxed structure in (001)/(100)-oriented epitaxial Pb(Zr,Ti)O <sub>3</sub> films grown on (100) SrTiO <sub>3</sub> substrates by metal organic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 014107	2.5	7
309	Characteristics of Undoped and Mn-Doped BiFeO <sub>3</sub> Films Formed on Pt and SrRuO <sub>3</sub> /Pt Electrodes by Radio-Frequency Sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KB02	1.4	15
308	One-axis Oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> and SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Films Prepared on Silicon Wafer by Chemical Solution Deposition Technique. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1199, 54		
307	Geometric Phase Analysis of Nano-Scale Strain Fields Around 90° Domains in PbTiO <sub>3</sub> /SrTiO <sub>3</sub> Epitaxial Thin Film. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1199, 12		2

306	Novel Highly Volatile MOCVD Precursors for Ta <sub>2</sub> O <sub>5</sub> and Nb <sub>2</sub> O <sub>5</sub> Thin Films. <i>ECS Transactions</i> , <b>2009</b> , 16, 243-251	1	6
305	Fabrication of conductive oxide polycrystalline BaPbO <sub>3</sub> films by chemical solution deposition and their electrical resistivity. <i>Journal of Electroceramics</i> , <b>2009</b> , 22, 78-81	1.5	2
304	Effect of film thickness on ferroelectric domain structure and properties of Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> /SrRuO <sub>3</sub> /SrTiO <sub>3</sub> heterostructures. <i>Journal of Materials Science</i> , <b>2009</b> , 44, 5318-5324	4.3	9
303	Orientation controlled deposition of Pb(Zr,Ti)O <sub>3</sub> films using a micron-size patterned SrRuO <sub>3</sub> buffer layer. <i>Journal of Materials Science</i> , <b>2009</b> , 44, 5339-5344	4.3	3
302	Deposition of undoped indium oxide thin films on stripe-patterned substrates by spray CVD. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 642-646	1.6	8
301	Effects of Substrate Clamping on Electrical Properties of Polycrystalline Piezoelectric Films. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KD09	1.4	11
300	Investigation of Oxygen Vacancies in Micro-Patterned PZT Thin Films Using Raman Spectroscopy. <i>Key Engineering Materials</i> , <b>2009</b> , 421-422, 135-138	0.4	
299	Influence of Pb and La contents on the lattice configuration of La-substituted Pb(Zr,Ti)O <sub>3</sub> films fabricated by CSD method. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , <b>2009</b> , 56, 687-92	3.2	1
298	Electronic and Structural Properties of BiZn <sub>0.5</sub> Ti <sub>0.5</sub> O <sub>3</sub> . <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 09KF05	1.4	14
297	Process-dependent coercive fields in undoped and Mn-doped BiFeO <sub>3</sub> films formed on SrRuCO <sub>3</sub> /Pt(111) electrodes by rf sputtering. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1199, 137		
296	Combinatorial preparation process of Pb(Zr <sub>1-x</sub> Ti <sub>x</sub> )O <sub>3</sub> thin films by chemical solution deposition method. <i>Journal of the Ceramic Society of Japan</i> , <b>2009</b> , 117, 698-702	1	9
295	Low strain sensitivity of the dielectric property of pyrochlore Bi <sub>2</sub> ZnNb <sub>2</sub> O <sub>10</sub> films. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 182901	3.4	11
294	Crystal Structure and Electrical Properties of {100}-Oriented Epitaxial BiCoO <sub>3</sub> /BiFeO <sub>3</sub> Films Grown by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7582-7585	1.4	34
293	Rhombohedral↔Tetragonal Phase Boundary with High Curie Temperature in (1-x)BiCoO <sub>3</sub> ↔BiFeO <sub>3</sub> Solid Solution. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7579-7581	1.4	83
292	Cubic-on-cubic growth of a MgO(001) thin film prepared on Si(001) substrate at low ambient pressure by the sputtering method. <i>Europhysics Letters</i> , <b>2008</b> , 81, 46001	1.6	16
291	Enhancement of ferroelectric and magnetic properties in BiFeO <sub>3</sub> films by small amount of cobalt addition. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 07E314	2.5	30
290	IN-SITU OBSERVATION OF STRAIN ACCUMULATION AND RELAXATION IN PbTiO <sub>3</sub> FILM DURING THERMAL PROCESS USING RAMAN SPECTROSCOPY. <i>Integrated Ferroelectrics</i> , <b>2008</b> , 99, 23-30	0.8	2
289	Growth of Epitaxial Potassium Niobate Film on (100)SrRuO <sub>3</sub> /(100)SrTiO <sub>3</sub> by Hydrothermal Method and their Electromechanical Properties. <i>Materials Research Society Symposia Proceedings</i> , <b>2008</b> , 1139, 1		1

288	Raman Spectroscopy Study of Oxygen Vacancies in PbTiO <sub>3</sub> Thin Films Generated Heat-Treated in Hydrogen Atmosphere. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7510-7513	1.4	16
287	Epitaxial Growth of Ferromagnetic Iron Silicide Thin Films on Silicon with Ytria-Stabilized Zirconia Buffer Layer. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 577-579	1.4	5
286	1 V saturated Pb(Zr,Ti)O <sub>3</sub> films with (111) orientation using lattice-matched (111)SrRuO <sub>3</sub> /(111)Pt bottom electrode prepared by pulsed metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 152901	3.4	10
285	Effect of the Annealing Temperature on Dielectric Properties of Bi <sub>1.5</sub> Zn <sub>1.0</sub> Nb <sub>1.5</sub> O <sub>7</sub> Films Prepared by MOCVD. <i>Key Engineering Materials</i> , <b>2008</b> , 388, 175-178	0.4	
284	Epitaxially grown ferroelectric thin films for memory applications (ferroelectric random access memories). <i>Phase Transitions</i> , <b>2008</b> , 81, 667-678	1.3	10
283	LangmuirBlodgett Fabrication of Nanosheet-Based Dielectric Films without an Interfacial Dead Layer. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7556-7560	1.4	23
282	Annealing Temperature Dependences of Ferroelectric and Magnetic Properties in Polycrystalline Co-Substituted BiFeO <sub>3</sub> Films. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7574-7578	1.4	19
281	In-Plane Rotated Crystal Structure in Continuous Growth of Bismuth Cuprate Superconducting Film. <i>Solid State Phenomena</i> , <b>2008</b> , 139, 53-58	0.4	
280	Temperature Dependency of Dielectric Properties in Epitaxially Grown SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Films with Different Orientation. <i>Key Engineering Materials</i> , <b>2008</b> , 368-372, 1811-1813	0.4	
279	Effect of Strain on Supercell Structure of Bismuth Cuprate Superconducting Film. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 664-666	1.4	
278	Electrooptic and Piezoelectric Properties of (Pb,La)(Zr,Ti)O <sub>3</sub> Films with Various Zr/Ti Ratios. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7541-7544	1.4	6
277	Preparation of (111)-Oriented SrRuO <sub>3</sub> /Pt Electrodes for Pb(Zr,Ti)O <sub>3</sub> -Based Ferroelectric Capacitors: Grain Size and Roughness Impact. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 1003-1007	1.4	2
276	Supercell Structure on Continuous Growth of Bi <sub>2</sub> Sr <sub>2</sub> Ca <sub>1</sub> Cu <sub>2</sub> O <sub>x</sub> Film. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 5602-5604	1.4	2
275	In-Plane Lattice Strain Evaluation in Piezoelectric Microcantilever by Two-Dimensional X-ray Diffraction. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7537-7540	1.4	11
274	Experimental evidence of strain relaxed domain structure in (100)/(001)-oriented epitaxial lead titanate thick films grown by metal organic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 064121	2.5	19
273	X-ray diffraction study of polycrystalline BiFeO <sub>3</sub> thin films under electric field. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 042907	3.4	6
272	Dimensionality-controlled insulator-metal transition and correlated metallic state in 5d transition metal oxides Sr <sub>n+1</sub> Ir <sub>n</sub> O <sub>3n+1</sub> (n=1, 2, and infinity). <i>Physical Review Letters</i> , <b>2008</b> , 101, 226402	7.4	354
271	Degradation-free dielectric property using bismuth layer-structured dielectrics having natural superlattice structure. <i>Journal of the Ceramic Society of Japan</i> , <b>2008</b> , 116, 1249-1254	1	12

270	Thick Epitaxial Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> Films Grown on (100)CaF <sub>2</sub> Substrates with Polar-Axis-Orientation. <i>Applied Physics Express</i> , <b>2008</b> , 1, 085001	2.4	28
269	Structural modulation in bismuth cuprate superconducting film with continuous epitaxial growth. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 1713-1717	1.6	2
268	Epitaxial growth of (1 0 0) Fe <sub>3</sub> Si thin films on insulating substrates. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 1703-1707	1.6	3
267	Morphology of sol-gel produced composite films for optical oxygen sensors. <i>Applied Surface Science</i> , <b>2008</b> , 254, 1545-1558	6.7	9
266	In situ gas-phase FTIR monitoring of liquid delivery MOCVD process for PZT film preparation. <i>Chemical Engineering Journal</i> , <b>2008</b> , 135, 10-14	14.7	
265	Single domain epitaxial growth of yttria-stabilized zirconia on Si(111) substrate. <i>Ceramics International</i> , <b>2008</b> , 34, 1047-1050	5.1	1
264	Step coverage study of indium-tin-oxide thin films by spray CVD on non-flat substrates at different temperatures. <i>Thin Solid Films</i> , <b>2008</b> , 516, 5864-5867	2.2	21
263	Tin oxide thin films deposited by spray CVD using ethanol solution of tin (II) chloride. <i>Transactions of the Materials Research Society of Japan</i> , <b>2008</b> , 33, 1363-1366	0.2	2
262	Crystal Structure Analysis of Epitaxial BiFeO <sub>3</sub> /BiCoO <sub>3</sub> Solid Solution Films Grown by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 6948-6951	1.4	44
261	Solution-Based Fabrication of High- $\kappa$ Dielectric Nanofilms Using Titania Nanosheets as a Building Block. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 6979-6983	1.4	9
260	Effect of source materials on film thickness and compositional uniformity of MOCVD-P(Zr,Ti)O <sub>3</sub> films. <i>Surface and Coatings Technology</i> , <b>2007</b> , 201, 9279-9284	4.4	2
259	BiFeSi <sub>2</sub> growth on Cu-mediated Si substrate and enhancement of photoluminescence. <i>Thin Solid Films</i> , <b>2007</b> , 515, 8144-8148	2.2	8
258	Satellite peaks amplified by modulation in bismuth cuprate thin film. <i>Physica C: Superconductivity and Its Applications</i> , <b>2007</b> , 463-465, 935-938	1.3	
257	Single-phase Pb(Zn <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> thin films grown by metalorganic chemical vapor deposition: Effects of growth sequence and substrates. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 495-499	1.6	2
256	Oxygen Content and Magnetic Properties of SrRuO <sub>3-<math>\delta</math></sub> Thin Films. <i>IEEE Transactions on Magnetics</i> , <b>2007</b> , 43, 3073-3075	2	2
255	Characterization of zinc-modified lithium tantalate thin films fabricated by chemical solution deposition method. <i>Journal of Sol-Gel Science and Technology</i> , <b>2007</b> , 42, 265-269	2.3	1
254	The Influence of Acceptor Doping on the Structure and Electrical Properties of Sol-Gel Derived BiFeO <sub>3</sub> Thin Films. <i>Ferroelectrics</i> , <b>2007</b> , 357, 35-40	0.6	27
253	Structural characterization by electronic transport properties on Fe <sub>3</sub> Si films. <i>Journal Physics D: Applied Physics</i> , <b>2007</b> , 40, 6873-6878	3	14

252	Impact of (111)-Oriented SrRuO <sub>3</sub> /Pt Tailored Electrode for Highly Reproducible Preparation of Metal Organic Chemical Vapour Deposited Pb(Zr,Ti)O <sub>3</sub> Films for High Density Ferroelectric Random Access Memory Applications. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 2139-2142	1.4	10
251	Analysis for crystal structure of Bi(Fe,Sc)O <sub>3</sub> thin films and their electrical properties. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 022906	3.4	56
250	1.54h photoluminescence from FeSi <sub>2</sub> as-deposited film. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 071903	3.4	22
249	Evaluation of Residual Strain and Oxygen Vacancy in Multilayer Ceramic Capacitor Using Laser Raman Spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 7005-7007	1.4	21
248	Strain and in-plane orientation effects on the ferroelectricity of (111)-oriented tetragonal Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> thin films prepared by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 222901	3.4	19
247	Domain structures in highly (100)-oriented epitaxial Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 064112	2.5	5
246	(111)-textured Mn-substituted BiFeO <sub>3</sub> thin films on SrRuO <sub>3</sub> /Pt/TiSiO <sub>2</sub> /Si structures. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 242914	3.4	37
245	Effect of the thermal expansion matching on the dielectric tunability of (100)-one-axis-oriented (Ba <sub>0.5</sub> Sr <sub>0.5</sub> )TiO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 142910	3.4	39
244	Enhancement of field-induced strain by La substitution in epitaxial Pb(Zr,Ti)O <sub>3</sub> films grown by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 262902	3.4	5
243	(111)-oriented Pb(Zr,Ti)O <sub>3</sub> films deposited on SrRuO <sub>3</sub> /Pt electrodes: Reproducible preparation by metal organic chemical vapor deposition, top electrode influence, and reliability. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 114105	2.5	5
242	Low-Temperature Preparation of Metallic Ruthenium Films by MOCVD Using Bis(2,4-dimethylpentadienyl)ruthenium. <i>Electrochemical and Solid-State Letters</i> , <b>2007</b> , 10, D60		26
241	RF Magnetron Sputtering Growth of Epitaxial SrRuO <sub>3</sub> Films with High Conductivity. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 6987-6990	1.4	37
240	Crystal structure and microstructure of epitaxial Pb(Zr,Ti)O <sub>3</sub> films consisting of mixed phases with tetragonal and rhombohedral symmetries grown on (100)cSrRuO <sub>3</sub> /(100)SrTiO <sub>3</sub> substrate by metalorganic chemical vapor deposition. <i>Journal of Materials Research</i> , <b>2007</b> , 22, 1551-1557	2.5	14
239	X-ray Analysis of Strain Relaxed Domain Structure in (100)/(001)-oriented epitaxial PbTiO <sub>3</sub> thick films grown on (100)SrTiO <sub>3</sub> substrates. <i>Materials Research Society Symposia Proceedings</i> , <b>2007</b> , 1034, 146		
238	Fabrication of ZnO Microstructures by Anisotropic Wet-Chemical Etching. <i>Journal of the Electrochemical Society</i> , <b>2007</b> , 154, D82	3.9	42
237	BOTTOM ELECTRODES DEPENDENCE OF FERROELECTRIC PROPERTIES IN EPITAXIAL BiFeO <sub>3</sub> /SrRuO <sub>3</sub> /SrTiO <sub>3</sub> STRUCTURES. <i>Integrated Ferroelectrics</i> , <b>2007</b> , 87, 42-49	0.8	1
236	Strain-relaxed structure in (001)/(100)-oriented epitaxial PbTiO <sub>3</sub> films grown on (100) SrTiO <sub>3</sub> substrates by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 112904	3.4	30
235	Probing intrinsic polarization properties in bismuth-layered ferroelectric films. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 112914	3.4	20



234	Effect of Oxygen Annealing on Ferroelectricity of BiFeO <sub>3</sub> Thin Films Formed by Pulsed Laser Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 3491-3494	1.4	19
233	Nanostructural Characterization of Surfaces, Interfaces, and Thinfilms using X-ray Reciprocal-Lattice Space Imaging. <i>Nihon Kessho Gakkaishi</i> , <b>2007</b> , 49, 292-299	0	1
232	MOCVD of Single-Axis c-Oriented Strontium Bismuth Titanate Thin Films and Their Electrical Properties. <i>Chemical Vapor Deposition</i> , <b>2006</b> , 12, 136-142		10
231	High- $\kappa$ Dielectric Nanofilms Fabricated from Titania Nanosheets. <i>Advanced Materials</i> , <b>2006</b> , 18, 1023-1027	2.4	184
230	Strong Dependence on Thickness of Room-Temperature Dielectric Constant of (100)-Oriented Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> Epitaxial Films Grown by Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L1074-L1076	1.4	2
229	Growth Behavior of c-Axis-Oriented Epitaxial SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Films on SrTiO <sub>3</sub> Substrates with Atomic Scale Step Structure. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L138-L141	1.4	8
228	Formation of BiFeO <sub>3</sub> /BiScO <sub>3</sub> Thin Films and Their Electrical Properties. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 7321-7324	1.4	10
227	Twin-Free Epitaxial Films Lateral Relation between YSZ(111) and Si(111). <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L1328-L1330	1.4	9
226	Site Occupancy Analysis on the Enhancement in Dy-Substituted Pb(Zr,Ti)O <sub>3</sub> Film. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 7548-7551	1.4	8
225	PROPERTIES OF A NOVEL BISMUTH PERCURSOR FOR MOCVD. <i>Integrated Ferroelectrics</i> , <b>2006</b> , 84, 197-208	2	
224	Formation of Stoichiometric SrRuO <sub>3</sub> Electrodes for PZT Capacitors by Pulsed-MOCVD. <i>Electrochemical and Solid-State Letters</i> , <b>2006</b> , 9, C164		1
223	Conformability of Ruthenium Dioxide Films Prepared on Substrates with Capacitor Holes by MOCVD and Modification by Annealing. <i>Electrochemical and Solid-State Letters</i> , <b>2006</b> , 9, C175		15
222	Seed Layer Free Conformal Ruthenium Film Deposition on Hole Substrates by MOCVD Using (2,4-Dimethylpentadienyl)(ethylcyclopentadienyl)ruthenium. <i>Electrochemical and Solid-State Letters</i> , <b>2006</b> , 9, C107		26
221	Ruthenium and Ruthenium Oxide Films Deposition by MOCVD Using Ru(DMPD) <sub>2</sub> . <i>ECS Transactions</i> , <b>2006</b> , 1, 139-144	1	3
220	Electrical Properties of Perovskite-Based Ferroelectric Thin Films Modified Using Rare-Earth Elements. <i>Key Engineering Materials</i> , <b>2006</b> , 320, 49-52	0.4	
219	Domain structures and piezoelectric properties in epitaxial Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 252904	3.4	25
218	Crystal structure, electrical properties, and mechanical response of (100)-/(001)-oriented epitaxial Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> /PbTiO <sub>3</sub> films grown on (100)cSrRuO <sub>3</sub> /(100)SrTiO <sub>3</sub> substrates by metal-organic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 054110	2.5	32
217	CRYSTAL ORIENTATION ANISOTROPY OF EPITAXIAL Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -PbTiO <sub>3</sub> THICK FILMS GROWN BY MOCVD. <i>Integrated Ferroelectrics</i> , <b>2006</b> , 80, 67-76	0.8	3



216	Strain-amplified structural modulation of Bi-cuprate high-T <sub>c</sub> superconductors. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	14
215	TRIAL FOR MAKING THREE DIMENSIONAL PZT CAPACITOR FOR HIGH DENSITY FERROELECTRIC RANDOM ACCESS MEMORY. <i>Integrated Ferroelectrics</i> , <b>2006</b> , 81, 219-226	0.8	2
214	Thickness dependence of dielectric properties in bismuth layer-structured dielectrics. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 082901	3.4	36
213	Effect of thermal treatment on oxygen stoichiometry and transport properties of SrRuO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 242115	3.4	12
212	Controlled crystal growth of layered-perovskite thin films as an approach to study their basic properties. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 051602	2.5	77
211	Conformality of Pb(Zr,Ti)O <sub>3</sub> Films Deposited on Trench Structures Having Submicrometer Diameter and Various Aspect Ratios. <i>Electrochemical and Solid-State Letters</i> , <b>2006</b> , 9, C15		11
210	INTRINSIC PROPERTIES OF (100)/(001)-ORIENTED EPITAXIAL PZT THIN FILMS GROWN ON (100)SI AND (100)SrTiO <sub>3</sub> SUBSTRATES. <i>Integrated Ferroelectrics</i> , <b>2006</b> , 78, 223-232	0.8	3
209	Epitaxial BiFeO <sub>3</sub> thin films fabricated by chemical solution deposition. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 162904	3.4	108
208	Structural Characterization of BiFeO <sub>3</sub> Thin Films by Reciprocal Space Mapping. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 7311-7314	1.4	70
207	Metalorganic Chemical Vapor Deposition of Epitaxial Perovskite SrIrO <sub>3</sub> Films on (100)SrTiO <sub>3</sub> Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L36-L38	1.4	33
206	INVESTIGATION OF Sr-Ru-O/Ru MULTILAYER-ELECTRODES PREPARED BY MOCVD. <i>Integrated Ferroelectrics</i> , <b>2006</b> , 81, 249-260	0.8	3
205	Crystal structure and ferroelectric properties of rare-earth substituted BiFeO <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 014106	2.5	215
204	A NEW METHOD TO CHARACTERIZE A RELATIVE VOLUME TO THE c-DOMAIN IN PZT FILMS BASED ON RAMAN SPECTRA. <i>Integrated Ferroelectrics</i> , <b>2006</b> , 78, 281-287	0.8	2
203	Horizontal growth of epitaxial (100) FeSi <sub>2</sub> templates by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2006</b> , 287, 694-697	1.6	3
202	Effect of template layer on formation of flat-surface FeSi <sub>2</sub> epitaxial films on (1 1 1) Si by metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2006</b> , 289, 37-43	1.6	7
201	Structural modulation in bismuth cuprate superconductor observed by X-ray reciprocal space mapping. <i>Journal of Crystal Growth</i> , <b>2006</b> , 287, 483-485	1.6	5
200	MOCVD growth of epitaxial pyrochlore Bi <sub>2</sub> Ti <sub>2</sub> O <sub>7</sub> thin film. <i>Journal of the European Ceramic Society</i> , <b>2006</b> , 26, 2155-2159	6	3
199	In situ FTIR investigation of the effect of gas-phase reaction on the deposition of Pb(Zr,Ti)O <sub>3</sub> films by MOCVD. <i>Thin Solid Films</i> , <b>2006</b> , 498, 277-281	2.2	4

198	Photoluminescence properties of Si/FeSi <sub>2</sub> /Si double heterostructure. <i>Thin Solid Films</i> , <b>2006</b> , 508, 380-384	42	6
197	Size Effect of Ferroelectric and High Permittivity Thin Films <b>2006</b> , 99-134		
196	LOCAL EPITAXIAL GROWTH OF TETRAGONAL (111)-ORIENTED Pb(Zr,Ti)O <sub>3</sub> THIN FILM. <i>Integrated Ferroelectrics</i> , <b>2005</b> , 75, 3-9	0.8	9
195	Raman Spectroscopic Characterization of Tetragonal PbZr <sub>x</sub> Ti <sub>1-x</sub> O <sub>3</sub> Thin Films: A Rapid Evaluation Method for Domain Volume. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L827-L829	1.4	17
194	Dependence of Ferroelectric Properties on Thickness of BiFeO <sub>3</sub> Thin Films Fabricated by Chemical Solution Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 8525-8527	1.4	45
193	Dependence of electrical properties of epitaxial Pb(Zr,Ti)O <sub>3</sub> thick films on crystal orientation and Zr/(Zr+Ti) ratio. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 094106	2.5	105
192	Effect of oxygen pressure on structural modulation observed by X-ray reciprocal space mapping in epitaxial bismuth cuprate superconducting film. <i>Europhysics Letters</i> , <b>2005</b> , 71, 686-691	1.6	3
191	Advanced X-ray Analysis of Ferroelectrics <b>2005</b> , 119-136		1
190	Polarization comparison of Pb(Zr,Ti)O <sub>3</sub> and Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> -based ferroelectrics. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2005</b> , 118, 23-27	3.1	9
189	Field-induced strain of (Pb, La)(Zr, Ti)O <sub>3</sub> epitaxial films grown by metal organic chemical vapor deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2005</b> , 120, 161-165	3.1	5
188	Phase Diagram and Microstructure in the ZnO-Bi <sub>2</sub> O <sub>3</sub> System. <i>Journal of the American Ceramic Society</i> , <b>2005</b> , 80, 995-998	3.8	18
187	Selective reaction and chemical anisotropy in epitaxial bismuth layer-structured ferroelectric thin films. <i>Journal of Solid State Chemistry</i> , <b>2005</b> , 178, 64-71	3.3	7
186	Micro-patterning of ZnO single crystal surface by anisotropic wet-chemical etching. <i>Thin Solid Films</i> , <b>2005</b> , 486, 42-45	2.2	20
185	MOCVD growth of epitaxial SrIrO <sub>3</sub> films on (111)SrTiO <sub>3</sub> substrates. <i>Thin Solid Films</i> , <b>2005</b> , 486, 182-185	2.2	22
184	THERMAL STABILITY OF EPITAXIAL SrRuO <sub>3</sub> BOTTOM ELECTRODES AND THEIR CONTRIBUTION TO THE CHARACTERISTICS OF (Ba <sub>0.5</sub> Sr <sub>0.5</sub> )TiO <sub>3</sub> FILMS GROWN ON THEM. <i>Integrated Ferroelectrics</i> , <b>2005</b> , 77, 3-11	0.8	2
183	Characteristic Comparison of Epitaxial PZT And PMN-PT Films Grown on (100)cSrRuO <sub>3</sub> /(100)SrTiO <sub>3</sub> Substrates By Metalorganic Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , <b>2005</b> , 902, 1		
182	Epitaxial Pt Films with Different Orientations Grown on (100)Si Substrates by RF Magnetron Sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 5102-5106	1.4	19
181	Orientation Dependence of Epitaxial and One-Axis-Oriented (Ba <sub>0.5</sub> Sr <sub>0.5</sub> )TiO <sub>3</sub> Films Prepared by RF Magnetron Sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 6881-6884	1.4	27

180	Structural and Electrical Properties of Polycrystalline Bi <sub>4-x</sub> Nd <sub>x</sub> Ti <sub>3</sub> O <sub>12</sub> Ferroelectric Thin Films with in-Plane c-Axis Orientations. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L292-L294	1.4	4
179	Photoluminescence Properties from BiFeSi <sub>2</sub> Film Epitaxially Grown on Si, YSZ and Si//YSZ. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L303-L305	1.4	21
178	Structural Modulation in Oxygen Deficient Epitaxial Bi <sub>2</sub> Sr <sub>2</sub> Ca <sub>1</sub> Cu <sub>2</sub> O <sub>x</sub> Observed by X-ray Reciprocal Space Mapping. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 156-157	1.4	3
177	Epitaxial Growth Map for Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> Films: a Determining Factor for Crystal Orientation. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 1337-1343	1.4	16
176	Crystal Structure and Electrical Properties of Epitaxial BiFeO <sub>3</sub> Thin Films Grown by Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L1231-L1233	1.4	50
175	MOCVD Growth of Bi <sub>1.5</sub> Zn <sub>1.0</sub> Nb <sub>1.5</sub> O <sub>7</sub> (BZN) Epitaxial Thin Films and Their Electrical Properties. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 6957-6959	1.4	16
174	Enhancement of Polarization Property of PZT Film by Ion-Substitution Using Rare-Earth Elements. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 6905-6909	1.4	11
173	Perovskite Single-Phase Growth of Epitaxial Pb(Zn <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> Films by Alternative-Source-Gas-Introduced Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L1452-L1455	1.4	4
172	Comparison of electrical properties of (100)/(001)-oriented epitaxial Pb(Zr <sub>0.35</sub> Ti <sub>0.65</sub> )O <sub>3</sub> thin films with the same (001) domain fraction grown on (100)Si and (100)SrTiO <sub>3</sub> substrates. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 182907	3.4	7
171	Structural modulation on multilayered bismuth cuprate observed by x-ray reciprocal space mapping. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 103904	2.5	15
170	Metalorganic chemical vapor deposition of atomically flat SrRuO <sub>3</sub> films on stepped SrTiO <sub>3</sub> substrates. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 052112	3.4	14
169	Domain distributions in tetragonal Pb(Zr,Ti)O <sub>3</sub> thin films probed by polarized Raman spectroscopy. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 232902	3.4	37
168	The effects of neodymium content and site occupancy on spontaneous polarization of epitaxial (Bi <sub>4-x</sub> Nd <sub>x</sub> )Ti <sub>3</sub> O <sub>12</sub> films. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 024110	2.5	23
167	Domain structure control of (001)/(100)-oriented epitaxial Pb(Zr,Ti)O <sub>3</sub> films grown on (100)cSrRuO <sub>3</sub> /(100)SrTiO <sub>3</sub> substrates. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 212905	3.4	23
166	Enhancement of spontaneous polarization in lead zirconate titanate thin films by Dy <sup>3+</sup> substitution. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 182906	3.4	12
165	Epitaxial Growth of (100)-Oriented BiFeSi <sub>2</sub> Thin Films on Insulating Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 2496-2501	1.4	5
164	Electric-Field-Induced Displacements in Pt/PZT/Pt/SiO <sub>2</sub> /Si System Investigated by Finite Element Method: Material-Constant Dependences. <i>Materials Research Society Symposia Proceedings</i> , <b>2005</b> , 902, 1		2
163	Dominant Factor of Squareness in P-E Hysteresis Loops of MOCVD-PZT Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2005</b> , 902, 1		

162	Ion Modification for Improvement of Insulating and Ferroelectric Properties of BiFeO <sub>3</sub> Thin Films Fabricated by Chemical Solution Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L561-L563	1.4	83
161	Dielectric Property Controls Using Crystal Structure Anisotropy in Bismuth Layer-Structured Dielectrics. <i>Materials Research Society Symposia Proceedings</i> , <b>2005</b> , 902, 1		
160	Site Engineering Concept of Ferroelectric Thin Films. <i>Hyomen Kagaku</i> , <b>2005</b> , 26, 215-219		3
159	Effect of Buffer Layer on Epitaxial Growth of YSZ Deposited on Si Substrate by Slower Q-switched 266 nm YAG Laser. <i>Japanese Journal of Applied Physics</i> , <b>2004</b> , 43, 1532-1535	1.4	13
158	Ferroelectric Properties of Dysprosium-Substituted Lead Zirconate Titanate Thin Films Fabricated by Chemical Solution Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2004</b> , 43, 6558-6561	1.4	8
157	Spontaneous Polarization of Neodymium-Substituted Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> Estimated from Epitaxially Grown Thin Films with in-Plane c-Axis Orientations. <i>Japanese Journal of Applied Physics</i> , <b>2004</b> , 43, L309-L311	1.4	20
156	Modulation derived satellite peaks in x-ray reciprocal mapping on bismuth cuprate superconductor film. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2301-2303	3.4	16
155	Thickness scaling of polycrystalline Pb(Zr,Ti)O <sub>3</sub> films down to 35 nm prepared by metalorganic chemical vapor deposition having good ferroelectric properties. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 1754-1756	3.4	22
154	Ferroelectric property of an epitaxial lead zirconate titanate thin film deposited by a hydrothermal method. <i>Journal of Materials Research</i> , <b>2004</b> , 19, 1862-1868	2.5	27
153	Crystal Orientation Dependence on Electrical Properties of Pb(Zr,Ti)O <sub>3</sub> Thick Films Grown on Si Substrates by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2004</b> , 43, 6567-6570	1.4	24
152	Effect of Solvent on MOCVD of Pb(Zr, Ti)O <sub>3</sub> Films with Liquid-Delivery Source Supply Method. <i>Journal of the Electrochemical Society</i> , <b>2004</b> , 151, C463	3.9	13
151	Effect of deposition temperature on the characteristics of hafnium oxide films deposited by metalorganic chemical vapor deposition using amide precursor. <i>Journal of Materials Research</i> , <b>2004</b> , 19, 584-589	2.5	10
150	Growth of Pyrochlore Bi <sub>2</sub> Ti <sub>2</sub> O <sub>7</sub> Epitaxial Films and Their Electrical Characterization. <i>Integrated Ferroelectrics</i> , <b>2004</b> , 67, 201-209	0.8	3
149	Effect of Deposition Temperature and Post-Heat-Treatment Condition on the Characteristics of (100)-Self-Oriented LaNiO <sub>3</sub> Films Prepared by RF Magnetron Sputter Deposition. <i>Materials Research Society Symposia Proceedings</i> , <b>2004</b> , 833, 57		3
148	Synthesis and Properties of Nd-Substituted Bismuth Titanate Polycrystalline Thin Films with Polar-Axis Orientation. <i>Key Engineering Materials</i> , <b>2004</b> , 269, 53-56	0.4	3
147	Growth of Epitaxial BiFeSi <sub>2</sub> Thin Film on Si(001) by Metal-Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2004</b> , 43, L551-L553	1.4	27
146	Comparison of the Ferroelectricity for 700 nm Thick Pb(Zr,Ti)O <sub>3</sub> Films Deposited on (111) Ir Bottom Electrodes at Different Temperatures by MOCVD. <i>Integrated Ferroelectrics</i> , <b>2004</b> , 68, 147-154	0.8	3
145	Source Gas Pulse-Introduced MOCVD of HfO <sub>2</sub> Thin Films using Hf(O-t-C[ <sub>4</sub> H[ <sub>9</sub> ])[ <sub>4</sub> ]. <i>Journal of the Electrochemical Society</i> , <b>2004</b> , 151, C698	3.9	4

144	Preparation of FeSi <sub>2</sub> thin film by metal organic chemical vapor deposition using iron-carbonyl and mono-silane. <i>Thin Solid Films</i> , <b>2004</b> , 461, 40-43	2.2	17
143	Comparison Study of (001)-/(100)-Oriented Epitaxial and Fiber-Textured Pb(Zr,Ti)O <sub>3</sub> Thick Films Prepared by MOCVD. <i>Integrated Ferroelectrics</i> , <b>2004</b> , 64, 217-225	0.8	4
142	Ferroelectric properties of an epitaxial lead zirconate titanate thin film deposited by a hydrothermal method below the Curie temperature. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 5094-5096	3.4	47
141	Spontaneous polarization change with Zr/(Zr+Ti) ratios in perfectly polar-axis-orientated epitaxial tetragonal Pb(Zr,Ti)O <sub>3</sub> films. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 3516-3518	3.4	56
140	Composition and orientation dependence of electrical properties of epitaxial Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> thin films grown using metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 3111-3115	2.5	63
139	Film Thickness Dependence of Electrical Properties for Pb(Zr,Ti)O <sub>3</sub> Thin Films Prepared on (111)Ir/TiO <sub>2</sub> /SiO <sub>2</sub> /Si and (111)Pt/TiO <sub>2</sub> /SiO <sub>2</sub> /Si Substrates by Pulsed-Metalorganic Chemical Vapor Deposition. <i>Integrated Ferroelectrics</i> , <b>2003</b> , 59, 1421-1428	0.8	1
138	Crystal Structure Analysis of Metalorganic Chemical Vapor Deposition-FeSi <sub>2</sub> Thin Film by X-ray Diffraction Measurement. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 4943-4948	1.4	16
137	Characterization of Hafnium Oxide Thin Films by Source Gas Pulse Introduced Metalorganic Chemical Vapor Deposition Using Amino-Family Hf Precursors. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 6015-6018	1.4	15
136	Film Thickness Dependence of Electrical Properties for Pb(Zr,Ti)O <sub>3</sub> Thin Films Prepared on (111)Ir/TiO <sub>2</sub> /SiO <sub>2</sub> /Si and (111)Pt/TiO <sub>2</sub> /SiO <sub>2</sub> /Si Substrates by Pulsed-Metalorganic Chemical Vapor Deposition. <i>Integrated Ferroelectrics</i> , <b>2003</b> , 59, 1421-1428	0.8	2
135	Quantitative Effects of Preferred Orientation and Impurity Phases on Ferroelectric Properties of SrBi <sub>2</sub> (Ta <sub>1-x</sub> Nb <sub>x</sub> ) <sub>2</sub> O <sub>9</sub> Thin Films Measured by X-Ray Diffraction Reciprocal Space Mapping. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 539-543	1.4	5
134	Bi <sub>3-x</sub> M <sub>x</sub> TiTaO <sub>9</sub> (M = La or Nd) Ceramics with High Mechanical Quality FactorQ <sub>m</sub> . <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 6090-6093	1.4	71
133	Electrical Properties of (Ca,Sr)Bi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Thin Films Fabricated Using a Chemical Solution Deposition Method. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 5990-5993	1.4	13
132	Compositional Dependence of Electrical Properties of Highly (100)-/(001)-Oriented Pb(Zr,Ti)O <sub>3</sub> Thick Films Prepared on Si Substrates by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 5922-5926	1.4	20
131	Good Ferroelectricity of Pb(Zr,Ti)O <sub>3</sub> Thin Films Fabricated by Highly Reproducible Deposition on Bottom Ir Electrode at 395°C. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L1083-L1086	1.4	7
130	Effect of La substitution on Electrical Properties of Highly Oriented Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> Films Prepared by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 166-169	1.4	22
129	Highly-Reproducible Preparation of Pb(Zr, Ti)O <sub>3</sub> Films at Low Deposition Temperature by Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 2801-2804	1.4	16
128	Self-Organized (100)-/(001)-Preferred Orientation in Pb(Zr,Ti)O <sub>3</sub> Films Grown on Polycrystalline Substrates by Metalorganic Chemical Vapor Deposition. <i>Integrated Ferroelectrics</i> , <b>2003</b> , 59, 1429-1436	0.8	8
127	Property design of Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> -based thin films using a site-engineered concept. <i>Journal of Crystal Growth</i> , <b>2003</b> , 248, 180-185	1.6	33



126	Preparation of hafnium oxide films from oxygen-free $\text{Hf}[\text{N}(\text{C}_2\text{H}_5)_2]_4$ precursor and their properties. <i>Applied Surface Science</i> , <b>2003</b> , 216, 296-301	6.7	12
125	Structural characterization and 90° domain contribution to ferroelectricity of epitaxial $\text{Pb}(\text{Zr}_{0.35}\text{Ti}_{0.65})\text{O}_3$ thin films. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 545-550	2.5	55
124	Large remanent polarization of 100% polar-axis-oriented epitaxial tetragonal $\text{Pb}(\text{Zr}_{0.35}\text{Ti}_{0.65})\text{O}_3$ thin films. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 4761-4763	3.4	62
123	Ferroelectric properties of lanthanide-substituted $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ epitaxial thin films grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 1707-1712	2.5	50
122	Fatigue-free $\text{RuO}_2/\text{Pb}(\text{Zr,Ti})\text{O}_3/\text{RuO}_2$ capacitor prepared by metalorganic chemical vapor deposition at 395 °C. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 5506-5508	3.4	40
121	Effect of Thermal Strain on Domain Fraction in a-/b-axis-oriented Epitaxial $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2003</b> , 784, 421		1
120	Property Improvement of MOCVD-PZT Films Deposited Below 400 °C. <i>Materials Research Society Symposia Proceedings</i> , <b>2003</b> , 784, 431		1
119	Ruthenium Film with High Nuclear Density Deposited by MOCVD Using a Novel Liquid Precursor. <i>Electrochemical and Solid-State Letters</i> , <b>2003</b> , 6, C117		43
118	Sample Geometry Effects on Electric-Field-Induced Displacements in Piezoelectric Thin Films Measured by Atomic Force Microscopy. <i>Materials Research Society Symposia Proceedings</i> , <b>2003</b> , 784, 11291		2
117	Growth of epitaxial tetragonal $\text{Pb}(\text{Zr,Ti})\text{O}_3$ thin films with 100% polar-axis-orientation and their electrical properties. <i>Materials Research Society Symposia Proceedings</i> , <b>2003</b> , 784, 621		2
116	Substrate effect on the crystal structure and ferroelectricity of low-temperature-deposited $\text{Pb}(\text{Zr,Ti})\text{O}_3$ thin films by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 4122-4124	3.4	14
115	Large piezoelectric response in (111)-oriented epitaxial $\text{Pb}(\text{Zr,Ti})\text{O}_3$ films consisting of mixed phases with rhombohedral and tetragonal symmetry. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 2408-2410	3.4	32
114	Highly-conducting indium-tin-oxide transparent films fabricated by spray CVD using ethanol solution of indium (III) chloride and tin (II) chloride. <i>Thin Solid Films</i> , <b>2002</b> , 409, 46-50	2.2	91
113	Room-temperature epitaxial growth of indium tin oxide thin films on Si substrates with an epitaxial $\text{CeO}_2$ ultrathin buffer. <i>Thin Solid Films</i> , <b>2002</b> , 415, 272-275	2.2	36
112	Orientation of $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ -based ferroelectric thin films prepared on various kinds of substrates by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2002</b> , 235, 389-393	1.6	13
111	Metal organic chemical vapor deposition growth of epitaxial $\text{SrRuO}_3$ and $\text{CaRuO}_3$ thin films with different orientations as the bottom electrode for epitaxial ferroelectric thin film. <i>Journal of Crystal Growth</i> , <b>2002</b> , 235, 401-406	1.6	27
110	Composition dependence of ferroelectric properties of epitaxial $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ thin films grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 455-458	1.6	20
109	Domain structures in epitaxial $\text{Pb}(\text{Zr}_{0.68}\text{Ti}_{0.32})\text{O}_3$ thin films. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 464-467	1.6	14



108	Preparation of $\text{SrBi}_2(\text{Ta}_{0.7}\text{Nb}_{0.3})_2\text{O}_9/\text{Bi}_3\text{TaTiO}_9$ solid solution films by MOCVD and their properties. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 473-477	1.6	3
107	Composition dependence of constituent phase of $\text{FeBi}$ thin film prepared by MOCVD. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 1951-1955	1.6	16
106	Effect of cosubstitution of La and V in $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ thin films on the low-temperature deposition. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 100-102	3.4	153
105	Comparison of crystal structure and electrical properties of tetragonal and rhombohedral $\text{Pb}(\text{Zr,Ti})\text{O}_3$ films prepared at low temperature by pulsed-metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 5448-5452	2.5	16
104	Effect of atmosphere during heating of substrate on the low temperature deposition of metalorganic chemical vapor deposited $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ thin films. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 898-900	3.4	14
103	Large remanent polarization of $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ -based thin films modified by the site engineering technique. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 1518-1521	2.5	82
102	Approach for enhanced polarization of polycrystalline bismuth titanate films by $\text{Nd}^{3+}/\text{V}^{5+}$ cosubstitution. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2229-2231	3.4	149
101	Ferroelectricity of one-axis-preferred-oriented polycrystalline $\text{Pb}(\text{Zr,Ti})\text{O}_3$ films prepared by pulsed-metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 6768-6772	2.5	17
100	Preparation and characterization of a- and b-axis-oriented epitaxially grown $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ -based thin films with long-range lattice matching. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1660-1662	3.4	94
99	Role of Non-180° Domain Switching in Electrical Properties of $\text{Pb}(\text{Zr}_{0.35}\text{Ti}_{0.65})\text{O}_3$ Thin Films. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 6730-6734	1.4	17
98	Thermal Stability of $\text{SrRuO}_3$ Bottom Electrode and Electric Property of $\text{Pb}(\text{Zr, Ti})\text{O}_3$ Thin Film Deposited on $\text{SrRuO}_3$ . <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 6873-6876	1.4	13
97	Fabrication of $\text{M}^{3+}$ -Substituted and $\text{M}^{3+}/\text{V}^{5+}$ -Cosubstituted Bismuth Titanate Thin Films [ $\text{M}=\text{lanthanoid}$ ] by Chemical Solution Deposition Technique. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 6820-6824	1.4	58
96	Preparation of Orientation-Controlled Polycrystalline $\text{Pb}(\text{Zr, Ti})\text{O}_3$ Thick Films on (100)Si Substrates by Metalorganic Chemical Vapor Deposition and Their Electrical Properties. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 6705-6708	1.4	19
95	Ferroelectric Property of a-/b-Axis-Oriented Epitaxial $\text{Sr}_{0.8}\text{Bi}_{2.2}\text{Ta}_2\text{O}_9$ Thin Films Grown by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L1478-L1481	1.4	11
94	Ferroelectricity of Epitaxial and Polycrystalline PZT Films Prepared by Pulsed-MOCVD. <i>Key Engineering Materials</i> , <b>2002</b> , 228-229, 69-74	0.4	1
93	Effect of Strain in Epitaxially Grown $\text{SrRuO}_3$ Thin Films on Crystal Structure and Electric Properties. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 5376-5380	1.4	41
92	New preparation process of $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ thin films from $\text{PbZrO}_3$ and $\text{PbTiO}_3$ multilayers. <i>Journal of Materials Research</i> , <b>2002</b> , 17, 2217-2226	2.5	9
91	A Novel Ruthenium Precursor for MOCVD without Seed Ruthenium Layer. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 748, 1		4

90	Characterization of Epitaxial Pb(Zrx,Ti1-x)O3 Thin Films with Composition Near the Morphotropic Phase Boundary. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 748, 1		8
89	Novel Candidate of c-axis-oriented BLSF Thin Films for High-Capacitance Condenser. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 748, 1		4
88	Growth of Epitaxial Site-Engineered Bi4Ti3O12-Basded Thin Films by Mocvdand Their Characterization. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 748, 1		
87	Long-Range Lattice Matching between (100)/(010) Bismuth-Layered Perovskite Structure and (101) Rutile Structure. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 748, 1		
86	Large remanent polarization of (Bi,Nd)4Ti3O12 epitaxial thin films grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 2746-2748	3.4	328
85	Preparation of SrBi 2 Ta 2 O 9 Thin Films by Liquid-Delivery MOCVD Without Additional Solvents. <i>Integrated Ferroelectrics</i> , <b>2002</b> , 45, 215-222	0.8	4
84	Characteristics of Pb(Zr, Ti)O3 thin films prepared on various substrates by source gas pulse-introduced metalorganic chemical vapor deposition. <i>Ferroelectrics</i> , <b>2001</b> , 260, 69-74	0.6	3
83	Residual strain analysis of epitaxial grown SBT thin films prepared by MOCVD. <i>Integrated Ferroelectrics</i> , <b>2001</b> , 33, 59-69	0.8	8
82	Effect of composition of MOCVD-SrRuO3 top electrode of (Pb, La)(Zr, Ti)O3 capacitor on H2 degradation. <i>Ferroelectrics</i> , <b>2001</b> , 260, 57-62	0.6	1
81	Preparation of Bi2WO6 thin films by metalorganic chemical vapor deposition and their electrical properties. <i>Thin Solid Films</i> , <b>2001</b> , 392, 128-133	2.2	23
80	Crystal structure comparison between conductive SrRuO3 and CaRuO3 thin films. <i>Journal of Crystal Growth</i> , <b>2001</b> , 229, 450-456	1.6	13
79	Low Temperature Preparation of High-Quality Pb(Zr, Ti)O3 Films by Metal Organic Chemical Vapor Deposition with High Reproducibility. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 688, 1		3
78	Low Temperature Deposition of Pb(Zr,Ti)O3 Film by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, L343-L345	1.4	24
77	Cation Distribution and Structural Instability in Bi4-xLaxTi3O12. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 5572-5575	1.4	143
76	Electrical Properties of Polycrystalline and Epitaxially Grown PZT Thin Films. <i>Key Engineering Materials</i> , <b>2001</b> , 216, 83-86	0.4	5
75	Ferroelectric property of epitaxial Bi4Ti3O12 films prepared by metalorganic chemical vapor deposition. <i>Journal of Materials Research</i> , <b>2001</b> , 16, 303-307	2.5	42
74	Conduction Mechanism of La-, Nb-Doped BaTiO3 Thin Films by Doping MOCVD. <i>Key Engineering Materials</i> , <b>2001</b> , 216, 87-92	0.4	1
73	Local Epitaxial Growth of (103) One-Axis-Oriented SrBi2Ta2O9Thin Films Prepared at Low Deposition Temperature by Metalorganic Chemical Vapor Deposition and Their Electrical Properties. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 5595-5598	1.4	16

72	Characterization of Ferroelectric Property of C-Axis- and Non-C-Axis-Oriented Epitaxially Grown Bi <sub>2</sub> VO <sub>5.5</sub> Thin Films. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 6481-6486	1.4	18
71	Preparation of Pb(Zr <sub>x</sub> , Ti <sub>1-x</sub> )O <sub>3</sub> Thin Films by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 4126-4130	1.4	31
70	Site definition and characterization of La-substituted Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> thin films prepared by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 6533-6535	2.5	38
69	Epitaxial-grade polycrystalline Pb(Zr,Ti)O <sub>3</sub> film deposited at low temperature by pulsed-metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 1000-1002	3.4	40
68	Film thickness dependence of ferroelectric properties of c-axis-oriented epitaxial Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> thin films prepared by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 3934-3938	3.5	67
67	Growth of FeSi <sub>2</sub> Thin Film on Si (111) by Metal-Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, L460-L462	1.4	36
66	Orientation dependence of ferroelectricity of epitaxially grown Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> thin films prepared by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 4517-4522	2.5	49
65	Hetero-epitaxial Growth of (1, 0, m+1) One Axis-oriented Bismuth Layered Structured Ferroelectrics Thin Films Directly Crystallized by MOCVD. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 688, 1		
64	Preparation and Characterization of a- and b-Axis-Oriented Epitaxially Grown Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> -Based Thin Films on Rutile-Type Oxides. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 688, 1		
63	Characterization of Ferroelectric Property of c-axis and non-c-axis Oriented Epitaxially Grown Bismuth Layer-Structured Ferroelectric Thin Films with Different m-numbers Prepared by MOCVD. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 655, 234		6
62	Preparations and Characterizations of Epitaxial SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 655, 48		
61	Property Improvement of PLZT Capacitor Using CaRuO <sub>3</sub> Top Electrode. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 655, 335		
60	Synthesis of New Liquid Mixed Sr <sub>1-x</sub> La <sub>x</sub> and Sr <sub>1-x</sub> Nb <sub>x</sub> Alkoxides as CVD Precursors for Metal Oxide Thin Films. <i>Chemical Vapor Deposition</i> , <b>2000</b> , 6, 225-227		13
59	Thermal Stability of Pb(C <sub>11</sub> H <sub>19</sub> O <sub>2</sub> ) <sub>2</sub> Used as the Lead Source in MOCVD. <i>Chemical Vapor Deposition</i> , <b>2000</b> , 6, 311-314		5
58	Preparation of bismuth layer-structured ferroelectric thin films by MOCVD and their characterization. <i>Advanced Materials for Optics and Electronics</i> , <b>2000</b> , 10, 193-200		18
57	Comparison of deposition behavior of Pb(Zr,Ti)O <sub>3</sub> films and its end-member-oxide films prepared by MOCVD. <i>Thin Solid Films</i> , <b>2000</b> , 368, 261-265	2.2	15
56	Metalorganic Chemical Vapor Deposition of Conductive CaRuO <sub>3</sub> Thin Films. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 2780-2783	1.4	23
55	Orientation Control of Metalorganic Chemical Vapor Deposition-Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> Thin Film by Sequential Source Gas Supply Method. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 5211-5216	1.4	21

54	Growth of Epitaxial SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Films by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 2102-2109	1.4	15
53	Improvement of Property of Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> Thin Film Prepared by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L996-L998	1.4	78
52	Preparation of Al-doped PbTiO <sub>3</sub> Thin Films by Metalorganic Chemical Vapor Deposition and Their Characterization. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 3591-3595	1.4	2
51	Low-Temperature Deposition of SrRuO <sub>3</sub> Thin Film Prepared by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 572-576	1.4	54
50	Crystal structure and electrical properties of epitaxial SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> films. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 8018-8023	2.5	35
49	Composition Control of Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> Thin Films Prepared by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 212-216	1.4	47
48	Method of Distinguishing SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Phase from Fluorite Phase Using X-Ray Diffraction Reciprocal Space Mapping. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 5489-5495	1.4	49
47	Preparation of SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Films by Metalorganic Chemical Vapor Deposition from Two New Liquid Organometallic Sources. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L199-L201	1.4	25
46	Effect of Deposition Temperature and Composition on the Microstructure and Electrical Property of SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Films Prepared by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 5428-5431	1.4	22
45	Interface and Domain Structures of (116)-Oriented SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Film Epitaxially Grown on (110) SrTiO <sub>3</sub> Single Crystal. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L1265-L1267	1.4	15
44	Interface and Defect Structures of (001)-Oriented SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Film Epitaxially Grown on (001) SrTiO <sub>3</sub> Single Crystal. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L1261-L1264	1.4	17
43	Metalorganic Chemical Vapor Deposition of Epitaxial SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Films and Their Crystal Structure. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L258-L260	1.4	15
42	CVD of SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> (SBT) Thin Film from Bi(CH <sub>3</sub> ) <sub>3</sub> - Sr[Ta(OC <sub>2</sub> H <sub>5</sub> ) <sub>6</sub> ] <sub>2</sub> - O <sub>2</sub> System. <i>Key Engineering Materials</i> , <b>1999</b> , 169-170, 145-148	0.4	6
41	Preparation and characterization of Pb(Nb,Ti)O <sub>3</sub> thin films by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 4559-4564	2.5	23
40	Orientation Control of ZnO Thin Film Prepared by CVD <b>1999</b> , 4, 25-32		32
39	Electrical properties of (001)- and (116)-oriented epitaxial SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> thin films prepared by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 1970-1972	3.4	78
38	Effects of growth conditions and RF plasma on crystalline and electrical properties of SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> thin films grown by liquid delivery MOCVD using a double alcoholate. <i>Integrated Ferroelectrics</i> , <b>1999</b> , 26, 109-117	0.8	1
37	Preparation of SrRuO <sub>3</sub> and CaRuO <sub>3</sub> Films by MOCVD and Its Application to Electrodes for Ferroelectric Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 596, 79		9

36	Deposition conditions of SrTiO <sub>3</sub> films on various substrates by CVD and their dielectric properties. <i>Thin Solid Films</i> , <b>1998</b> , 334, 71-76	2.2	5
35	Preparation of PbTiO <sub>3</sub> thin film by laser-assisted cvd and its electrical properties. <i>Integrated Ferroelectrics</i> , <b>1998</b> , 20, 159-172	0.8	
34	Diffusion of Bi into ZnO Film Prepared by CVD and Its I-V Characteristics. <i>Key Engineering Materials</i> , <b>1998</b> , 157-158, 175-180	0.4	1
33	Y <sub>2</sub> O <sub>3</sub> -Stabilized ZrO <sub>2</sub> Thin Films Prepared by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 6229-6232	1.4	34
32	Electrical properties of semiconductive Nb-doped BaTiO <sub>3</sub> thin films prepared by metalorganic chemical-vapor deposition. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 2017-2019	3.4	34
31	Crystal structure and dielectric property of epitaxially grown (Ba, Sr)TiO <sub>3</sub> thin film prepared by molecular chemical vapor deposition. <i>Journal of Materials Research</i> , <b>1998</b> , 13, 3512-3518	2.5	14
30	Preparation of semiconductive SrTiO <sub>3</sub> thin films by metal-organic chemical vapor deposition and their electrical properties. <i>Journal of Materials Research</i> , <b>1997</b> , 12, 1655-1660	2.5	9
29	Residual Strain and Crystal Structure ofBaTiO <sub>3</sub> BrTiO <sub>3</sub> Thin Films Prepared by Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 5879-5884	1.4	22
28	Effect of calcium modification on the microstructure and oxidation property of submicron spherical palladium powders. <i>Journal of Materials Research</i> , <b>1997</b> , 12, 392-397	2.5	8
27	Evolution of Particle Structure during the Formation of Single-Crystal Spherical Palladium Particles by Spray Pyrolysis. <i>Journal of the Ceramic Society of Japan</i> , <b>1997</b> , 105, 299-303		7
26	The Effect of Ti/Sr Ratio on Grain Growth of La-Doped SrTiO <sub>3</sub> Ceramics. <i>Journal of the Ceramic Society of Japan</i> , <b>1996</b> , 104, 190-195		4
25	Preparation of Semiconductive Epitaxial BaTiO <sub>3</sub> Thin Film and its Electrical Properties. <i>Journal of the Ceramic Society of Japan</i> , <b>1996</b> , 104, 75-77		8
24	Modification of semiconductive BaTiO <sub>3</sub> film and its electrical properties. <i>Materials Research Bulletin</i> , <b>1996</b> , 31, 1233-1241	5.1	4
23	General rule for the determination of c-axis orientation of Pb-based tetragonal ferroelectric oxide film prepared by CVD. <i>Journal of Materials Science Letters</i> , <b>1995</b> , 14, 629-632		6
22	Effect of KrF excimer laser irradiation on low-temperature preparation of lead titanium oxide film by metalorganic chemical vapor deposition. <i>Materials Research Bulletin</i> , <b>1995</b> , 30, 1081-1088	5.1	6
21	Formability and Sinterability of Hydrothermally Crystallized Monodispersed Titanium Dioxide Particles. <i>Journal of the Ceramic Society of Japan</i> , <b>1995</b> , 103, 552-556		5
20	Residual Strain in Epitaxially-grown PbTiO <sub>3</sub> and PZT Films Prepared on (100)MgO Substrates by MOCVD.. <i>Nippon Kagaku Kaishi / Chemical Society of Japan - Chemistry and Industrial Chemistry Journal</i> , <b>1995</b> , 1995, 789-795		3
19	Characterization of Epitaxially Grown CVD-Pb(Zr, Ti) O <sub>3</sub> Films with High Deposition Rate. <i>Journal of the Ceramic Society of Japan</i> , <b>1994</b> , 102, 114-118		7



18	Deposition Condition of Epitaxially Grown PZT Films by CVD. <i>Journal of the Ceramic Society of Japan</i> , <b>1994</b> , 102, 795-798		6
17	Preparation of PZT Film on (100)Pt/(100) MgO Substrate by CVD and Its Properties. <i>Journal of the Ceramic Society of Japan</i> , <b>1994</b> , 102, 128-132		6
16	Film Thickness Dependence of Dielectric Property and Crystal Structure of PbTiO <sub>3</sub> Film Prepared on Pt/SiO <sub>2</sub> /Si Substrate by Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, 4175-4178	1.4	49
15	Microstructure of Iron Nitride-Titanium Nitride Films Prepared by CVD. <i>Journal of the Ceramic Society of Japan</i> , <b>1993</b> , 101, 733-736		1
14	Preparation of FeN <sub>x</sub> -TiN films by CVD. <i>Journal of Materials Science</i> , <b>1993</b> , 28, 994-998	4.3	
13	Grain Boundary Structure of Bi <sub>2</sub> O <sub>3</sub> -Diffused BaTiO <sub>3</sub> BL Capacitor. <i>Journal of the Ceramic Society of Japan</i> , <b>1992</b> , 100, 1266-1270		0
12	Formation of Epitaxial Pb(Zr, Ti)O <sub>3</sub> Film by CVD. <i>Journal of the Ceramic Society of Japan</i> , <b>1991</b> , 99, 248-250		19
11	Growth of Epitaxial PLZT Film by CVD. <i>Journal of the Ceramic Society of Japan</i> , <b>1991</b> , 99, 1169-1171		10
10	Preparation of TaN <sub>x</sub> -TiN Films by CVD. <i>Journal of the Ceramic Society of Japan</i> , <b>1990</b> , 98, 168-173		4
9	Preparation and deposition mechanism of tantalum nitride films by CVD.. <i>Kagaku Kogaku Ronbunshu</i> , <b>1990</b> , 16, 430-437	0.4	1
8	Deposition characteristics and properties of iron nitride films by CVD using organometallic compound. <i>Journal of Materials Science</i> , <b>1990</b> , 25, 5303-5312	4.3	5
7	Preparation of iron nitride films from organometallic compound. <i>Journal of Materials Science Letters</i> , <b>1988</b> , 7, 851-852		4
6	Preparation of Niobium Nitride Films by CVD. <i>Journal of the Ceramic Association Japan</i> , <b>1987</b> , 95, 65-68		1
5	No-Heating Deposition of 1- $\mu$ m-Thick Y-Doped HfO <sub>2</sub> Ferroelectric Films with Good Ferroelectric and Piezoelectric Properties by Radio Frequency Magnetron Sputtering Method. <i>Physica Status Solidi - Rapid Research Letters</i> , 2100574	2.5	0
4	Effect of Film Microstructure on Domain Nucleation and Intrinsic Switching in Ferroelectric Y:HfO <sub>2</sub> Thin Film Capacitors. <i>Advanced Functional Materials</i> , 2108876	15.6	3
3	Linear electro-optic effect in ferroelectric HfO <sub>2</sub> -based epitaxial thin films. <i>Japanese Journal of Applied Physics</i> ,	1.4	3
2	Influence of orientation on the electro-optic effect in epitaxial Y-doped HfO <sub>2</sub> ferroelectric thin films. <i>Japanese Journal of Applied Physics</i> ,	1.4	2
1	Capacitor Applications of c-Axis-Oriented Bismuth Layer Structured Ferroelectric Thin Films. <i>Ceramic Engineering and Science Proceedings</i> , 57-64	0.1	3

